## 1. INTRODUCTION

SPICE is a general-purpose circuit simulation program for nonlinear dc, nonlinear transient, and linear ac analyses. Circuits may contain resistors, capacitors, inductors, mutual inductors, independent voltage and current sources, four types of dependent sources, lossless and lossy transmission lines (two seperate implementations), switches, uniform distributed RC lines, and the five most common semiconductor devices: diodes, BJTs, JFETs, MESFETs, and MOSFETs.

The SPICE3 version is based directly on SPICE 2G.6. While SPICE3 is being developed to include new features, it continues to support those capabilities and models which remain in extensive use in the SPICE2 program.

SPICE has built-in models for the semiconductor devices, and the user need specify only the pertinent model parameter values. The model for the BJT is based on the integral-charge model of Gummel and Poon; however, if the Gummel- Poon parameters are not specified, the model reduces to the simpler Ebers-Moll model. In either case, charge-storage effects, ohmic resistances, and a current-dependent output conductance may be included. The diode model can be used for either junction diodes or Schottky barrier diodes. The JFET model is based on the FET model of Shichman and Hodges. Six MOSFET models are implemented: MOS1 is described by a square-law I-V characteristic, MOS2[1] is an analytical model, while MOS3[1] is a semi-empirical model; MOS6[2] is a simple analytic model accurate in the short channel region; MOS4[3, 4] and MOS5[5] are the BSIM (Berkeley Short-channel IGFET Model) and BSIM2. MOS2, MOS3, and MOS4 include second-order effects such as channel length modulation, subthreshold conduction, scattering-limited velocity saturation, small-size effects, and charge-controlled capacitances.

# 2. TYPES OF ANALYSIS

## 2.1. DC Analysis

The dc analysis portion of SPICE determines the dc operating point of the circuit with inductors shorted and capacitors opened. The dc analysis options are specified on the .DC, .TF, and .OP control lines. A dc analysis is automatically performed prior to a transient analysis to determine the transient initial conditions, and prior to an ac small-signal analysis to determine the linearized, small-signal models for nonlinear devices. If requested, the dc small-signal value of a transfer function (ratio of output variable to input source), input resistance, and output resistance is also computed as a part of the dc solution. The dc analysis can also be used to generate dc transfer curves: a specified independent voltage or current source is stepped over a user-specified range and the dc output variables are stored for each sequential source value.

## 2.2. AC Small-Signal Analysis

The ac small-signal portion of SPICE computes the ac output variables as a function of frequency. The program first computes the dc operating point of the circuit and determines linearized, small-signal models for all of the nonlinear devices in the circuit. The resultant linear circuit is then analyzed over a user-specified range of frequencies. The desired output of an ac small- signal analysis is usually a transfer function (voltage gain, transimpedance, etc). If the circuit has only one ac input, it is convenient to set that input to unity and zero phase, so that output variables have the same value as the transfer function of the output variable with respect to the input.

## 2.3. Transient Analysis

The transient analysis portion of SPICE computes the transient output variables as a function of time over a user-specified time interval. The initial conditions are automatically determined by a dc analysis. All sources which are not time dependent (for example, power supplies) are set to their dc value. The transient time interval is specified on a .TRAN control line.

## 2.4. Pole-Zero Analysis

The pole-zero analysis portion of SPICE computes the poles and/or zeros in the small-signal ac transfer function. The program first computes the dc operating point and then determines the linearized, small-signal models for all the nonlinear devices in the circuit. This circuit is then used to find the poles

and zeros of the transfer function.

Two types of transfer functions are allowed : one of the form (output voltage)/(input voltage) and the other of the form (output voltage)/(input current). These two types of transfer functions cover all the cases and one can find the poles/zeros of functions like input/output impedance and voltage gain. The input and output ports are specified as two pairs of nodes.

The pole-zero analysis works with resistors, capacitors, inductors, linear-controlled sources, independent sources, BJTs, MOSFETs, JFETs and diodes. Transmission lines are not supported.

## 2.5. Small-Signal Distortion Analysis

The distortion analysis portion of SPICE computes steady-state harmonic and intermodulation products for small input signal magnitudes. If signals of a single frequency are specified as the input to the circuit, the complex values of the second and third harmonics are determined at every point in the circuit. If there are signals of two frequencies input to the circuit, the analysis finds out the complex values of the circuit variables at the sum and difference of the input frequencies, and at the difference of the smaller frequency from the second harmonic of the larger frequency.

Distortion analysis is supported for the following nonlinear devices: DIO, BJT, JFET, MOSFETs (levels 1, 2, 3 and BSIM) and MESFETS. All linear devices are automatically supported by distortion analysis. If there are switches present in the circuit, the analysis continues to be accurate provided the switches do not change state under the small excitations used for distortion calculations.

## 2.6. Noise Analysis

The noise analysis portion of SPICE does analysis device-generated noise for the given circuit. When provided with an input source and an output port, the analysis calculates the noise contributions of each device (and each noise generator within the device) to the output port voltage. It also calculates the input noise to the circuit, equivalent to the output noise referred to the specified input source. This is done for every frequency point in a specified range - the calculated value of the noise corresponds to the spectral density of the circuit variable viewed as a stationary gaussian stochastic process.

After calculating the spectral densities, noise analysis integrates these values over the specified frequency range to arrive at the total noise voltage/current (over this frequency range). This calculated value corresponds to the variance of the circuit variable viewed as a stationary gaussian process.

## 2.7. Analysis at Different Temperatures

All input data for SPICE is assumed to have been measured at a nominal temperature of 27°C, which can be changed by use the the TNOM parameter on the .OPTION control line. This value can further be

overridden for any device which models temperature effects by specifying the TNOM parameter on the model itself. The circuit simulation is performed at a temperature of 27°C, unless overridden by a TEMP parameter on the .OPTION control line. Individual instances may further override the circuit temperature through the specification of a TEMP parameter on the instance.

Temperature dependent support is provided for resistors, diodes, JFET's, BJT's, and level 1, 2, and 3 MOSFET's. BSIM (level 4) MOSFET's have an alternate temperature dependency scheme which adjusts all of the model parameters before input to SPICE. For details of the BSIM temperature adjustment, see [7] or [8].

Temperature appears explicitly in the exponential terms of the BJT and diode model equations. In addition, saturation currents have a built-in temperature dependence. The temperature dependence of the saturation current in the BJT models is determined by:

$$I_S(T_1) = I_S(T_0) \left( \frac{T_1}{T_0} \right)^{XTI} \exp\left( \frac{E_g q (T_1\ T_0)}{k\ (T_1 - T_0)} \right)$$

where k is Boltzmann's constant, q is the electronic charge, $E_G$ is the energy gap which is a model parameter, and XTI is the saturation current temperature exponent (also a model parameter, and usually equal to 3).

The temperature dependence of forward and reverse beta is according to the formula:

$$\beta(T_1) = \beta(T_0) \left( \frac{T_1}{T_0} \right)^{XTB}$$

where $T_1$ and $T_0$ are in degrees Kelvin, and XTB is a user-supplied model parameter. Temperature effects on beta are carried out by appropriate adjustment to the values of $\beta_F$, $I_{SE}$, $\beta_R$, and $I_{SC}$ (spice model parameters BF, ISE, BR, and ISC, respectively).

Temperature dependence of the saturation current in the junction diode model is determined by:

$$I_S(T_1) = I_S(T_0) \left( \frac{T_1}{T_0} \right)^{\frac{XTI}{N}} \exp\left( \frac{E_g q (T_1\ T_0)}{N\ k\ (T_1 - T_0)} \right)$$

where N is the emission coefficient, which is a model parameter, and the other symbols have the same meaning as above. Note that for Schottky barrier diodes, the value of the saturation current temperature exponent, XTI, is usually 2.

Temperature appears explicitly in the value of junction potential, $\phi$ (in spice PHI), for all the device models. The temperature dependence is determined by:

$$\phi(T) = \frac{kT}{q}\log_e\left(\frac{N_a N_d}{N_i(T)^2}\right)$$

where k is Boltzmann's constant, q is the electronic charge, $N_a$ is the acceptor impurity density, $N_d$ is the donor impurity density, $N_i$ is the intrinsic carrier concentration, and $E_g$ is the energy gap.

Temperature appears explicitly in the value of surface mobility, $\mu_0$ (or UO), for the MOSFET model. The temperature dependence is determined by:

$$\mu_0(T) = \frac{\mu_0(T_0)}{\left(\frac{T}{T_0}\right)^{1.5}}$$

The effects of temperature on resistors is modeled by the formula:

$$R(T) = R(T_0)\,[1 + TC_1\,(T - T_0) + TC_2\,(T - T_0)^2]$$

where T is the circuit temperature, $T_0$ is the nominal temperature, and $TC_1$ and $TC_2$ are the first- and second-order temperature coefficients.

## 3. CONVERGENCE

Both dc and transient solutions are obtained by an iterative process which is terminated when both of the following conditions hold:

1) The nonlinear branch currents converge to within a tolerance of 0.1 percent or 1 picoamp (1.0e-12 Amp), whichever is larger.

2) The node voltages converge to within a tolerance of 0.1 percent or 1 microvolt (1.0e-6 Volt), whichever is larger.

Although the algorithm used in SPICE has been found to be very reliable, in some cases it fails to converge to a solution. When this failure occurs, the program terminates the job.

Failure to converge in dc analysis is usually due to an error in specifying circuit connections, element values, or model parameter values. Regenerative switching circuits or circuits with positive feedback probably will not converge in the dc analysis unless the OFF option is used for some of the devices in the feedback path, or the .NODESET control line is used to force the circuit to converge to the desired state.

## 4. INPUT FORMAT

The input format for SPICE is of the free format type. Fields on a line are separated by one or more blanks, a comma, an equal ('=') sign, or a left or right parenthesis; extra spaces are ignored. A line may be continued by entering a '+' (plus) in column 1 of the following line; SPICE continues reading beginning with column 2.

A name field must begin with a letter (A through Z) and cannot contain any delimiters.

A number field may be an integer field (12, -44), a floating point field (3.14159), either an integer or floating point number followed by an integer exponent (1e-14, 2.65e3), or either an integer or a floating point number followed by one of the following scale factors:

| | | | | |
|---|---|---|---|---|
| $T = 10^{12}$ | $G = 10^{9}$ | $Meg = 10^{6}$ | $K = 10^{3}$ | $mil = 25.4^{-6}$ |
| $m = 10^{-3}$ | $u$ (or $\mu$) $= 10^{-6}$ | $n = 10^{-9}$ | $p = 10^{-12}$ | $f = 10^{-15}$ |

Letters immediately following a number that are not scale factors are ignored, and letters immediately following a scale factor are ignored. Hence, 10, 10V, 10Volts, and 10Hz all represent the same number, and M, MA, MSec, and MMhos all represent the same scale factor. Note that 1000, 1000.0, 1000Hz, 1e3, 1.0e3, 1KHz, and 1K all represent the same number.

## 5. CIRCUIT DESCRIPTION

The circuit to be analyzed is described to SPICE by a set of element lines, which define the circuit topology and element values, and a set of control lines, which define the model parameters and the run controls. The first line in the input file must be the title, and the last line must be ".END". The order of the remaining lines is arbitrary (except, of course, that continuation lines must immediately follow the line being continued).

Each element in the circuit is specified by an element line that contains the element name, the circuit nodes to which the element is connected, and the values of the parameters that determine the electrical characteristics of the element. The first letter of the element name specifies the element type. The format for the SPICE element types is given in what follows. The strings XXXXXXX, YYYYYYY, and ZZZZZZZ denote arbitrary alphanumeric strings. For example, a resistor name must begin with the letter R and can contain one or more characters. Hence, R, R1, RSE, ROUT, and R3AC2ZY are valid resistor names.

Data fields that are enclosed in less than and greater than signs '< >' are optional. All indicated punctuation (parentheses, equal signs, etc.) is optional and merely indicate the presence of any delimiter. A consistent style such as that shown here makes the input easier to understand. With respect to branch voltages and currents, SPICE uniformly uses the associated reference convention (current flows in the direction of voltage drop).

Nodes names may be arbitrary character strings. The datum (ground) node must be named '0'. Note the difference in SPICE3 where the nodes are treated as character strings and not evaluated as numbers, thus '0' and '00' are distinct nodes in SPICE3 but not in SPICE2. The circuit cannot contain a loop of voltage sources and/or inductors and cannot contain a cutset of current sources and/or capacitors. Each node in the circuit must have a dc path to ground. Every node must have at least two connections except for transmission line nodes (to permit unterminated transmission lines) and MOSFET substrate nodes (which have two internal connections anyway).

# 6. TITLE LINE, COMMENT LINES AND .END LINE

## 6.1. Title Line

**Examples:**

```
POWER AMPLIFIER CIRCUIT
TEST OF CAM CELL
```

This line must be the first in the input deck. Its contents are printed verbatim as the heading for each section of output.

## 6.2. .END Line

**Examples:**

```
.END
```

This line must always be the last in the input deck. Note that the period is an integral part of the name.

## 6.3. Comment Line

**General Form:**

```
* <any comment>
```

**Examples:**

```
* RF=1K      GAIN SHOULD BE 100
* MAY THE FORCE BE WITH MY CIRCUIT
```

The asterisk in the first column indicates that this line is a comment line. Comment lines may be placed anywhere in the circuit description. Note that SPICE3 also considers any line with leading white space to be a comment.

# 7. ELEMENT LINES

## 7.1. Resistors

**General form:**

```
RXXXXXXX N1 N2 VALUE
```

**Examples:**

```
R1 1 2 100
RC1 12 17 1K
```

N1 and N2 are the two element nodes. VALUE is the resistance (in ohms) and may be positive or negative but not zero.

## 7.2. Capacitors and Inductors

**General form:**

```
CXXXXXXX N+ N- VALUE <IC=INCOND>
LYYYYYYY N+ N- VALUE <IC=INCOND>
```

**Examples:**

```
CBYP 13 0 1UF
COSC 17 23 10U IC=3V
LLINK 42 69 1UH
LSHUNT 23 51 10U IC=15.7MA
```

N+ and N- are the positive and negative element nodes, respectively. VALUE is the capacitance in Farads or the inductance in Henries.

For the capacitor, the (optional) initial condition is the initial (time-zero) value of capacitor voltage (in Volts). For the inductor, the (optional) initial condition is the initial (time-zero) value of inductor current (in Amps) that flows from N+, through the inductor, to N-. Note that the initial conditions (if any) apply 'only' if the UIC option is specified on the .TRAN control line.

### 7.3. Coupled (Mutual) Inductors

**General form:**

```
KXXXXXXX LYYYYYYY LZZZZZZZ VALUE
```

**Examples:**

```
K43 LAA LBB 0.999
KXFRMR L1 L2 0.87
```

LYYYYYYY and LZZZZZZZ are the names of the two coupled inductors, and VALUE is the coefficient of coupling, K, which must be greater than 0 and less than or equal to 1. Using the 'dot' convention, place a 'dot' on the first node of each inductor.

### 7.4. Transmission Lines (Lossless)

**General form:**

```
TXXXXXXX N1 N2 N3 N4 Z0=VALUE <TD=VALUE> <F=FREQ <NL=NRMLEN>>
+                    <IC=V1, I1, V2, I2>
```

**Examples:**

```
T1 1 0 2 0 Z0=50 TD=10NS
```

N1 and N2 are the nodes at port 1; N3 and N4 are the nodes at port 2. Z0 is the characteristic impedance. The length of the line may be expressed in either of two forms. The transmission delay, TD, may be specified directly (as TD=10ns, for example). Alternatively, a frequency F may be given, together with NL, the normalized electrical length of the transmission line with respect to the wavelength in the line at the frequency F. If a frequency is specified but NL is omitted, 0.25 is assumed (that is, the frequency is assumed to be the quarter-wave frequency). Note that although both forms for expressing the line length are indicated as optional, one of the two must be specified.

Note that this element models only one propagating mode. If all four nodes are distinct in the actual circuit, then two modes may be excited. To simulate such a situation, two transmission-line elements are required. (see the example in Appendix A for further clarification.)

The (optional) initial condition specification consists of the voltage and current at each of the transmission line ports. Note that the initial conditions (if any) apply 'only' if the UIC option is specified on the .TRAN control line.

Note that a lossy transmission line (see below) with zero loss may be more accurate than than the lossless transmission line due to implementation details.

### 7.5. Lossy Transmission Lines

**General form:**

```
OXXXXXXX N1 N2 N3 N4 MNAME
```

**Examples:**

```
O23 1 0 2 0 LOSSYMOD
OCONNECT 10 5 20 5 INTERCONNECT
```

This is a two-port convolution model for single-conductor lossy transmission lines. N1 and N2 are the nodes at port 1; N3 and N4 are the nodes at port 2. Note that a lossy transmission line with zero loss may be more accurate than than the lossless transmission line due to implementation details.

For further details, see the description of the LTRA type of the .MODEL card.

### 7.6. Linear Dependent Sources

SPICE allows circuits to contain linear dependent sources characterized by any of the four equations

$i = g\,v \qquad v = e\,v \qquad i = f\,i \qquad v = h\,i$

where g, e, f, and h are constants representing transconductance, voltage gain, current gain, and transresistance, respectively.

#### 7.6.1. Linear Voltage-Controlled Current Sources

**General form:**

```
GXXXXXXX N+ N- NC+ NC- VALUE
```

**Examples:**

```
G1 2 0 5 0 0.1MMHO
```

N+ and N- are the positive and negative nodes, respectively. Current flow is from the positive node, through the source, to the negative node. NC+ and NC- are the positive and negative controlling nodes, respectively. VALUE is the transconductance (in mhos).

### 7.6.2. Linear Voltage-Controlled Voltage Sources

**General form:**

```
EXXXXXXX N+ N- NC+ NC- VALUE
```

**Examples:**

```
E1 2 3 14 1 2.0
```

N+ is the positive node, and N- is the negative node. NC+ and NC- are the positive and negative controlling nodes, respectively. VALUE is the voltage gain.

### 7.6.3. Linear Current-Controlled Current Sources

**General form:**

```
FXXXXXXX N+ N- VNAM VALUE
```

**Examples:**

```
F1 13 5 VSENS 5
```

N+ and N- are the positive and negative nodes, respectively. Current flow is from the positive node, through the source, to the negative node. VNAM is the name of a voltage source through which the controlling current flows. The direction of positive controlling current flow is from the positive node, through the source, to the negative node of VNAM. VALUE is the current gain.

### 7.6.4. Linear Current-Controlled Voltage Sources

**General form:**

```
HXXXXXXX N+ N- VNAM VALUE
```

**Examples:**

```
HX 5 17 VZ 0.5K
```

N+ and N- are the positive and negative nodes, respectively. VNAM is the name of a voltage source through which the controlling current flows. The direction of positive controlling current flow is from the positive node, through the source, to the negative node of VNAM. VALUE is the transresistance (in ohms).

### 7.7. Non-linear Dependent Sources

**General form:**

```
BXXXXXXX N+ N- <I=EXPR> <V=EXPR>
```

**Examples:**

```
B1 0 1 I=cos(v(1))+sin(v(2))
B1 0 1 V=ln(cos(log(v(1,2)^2)))-v(3)^4+v(2)^v(1)
B1 3 4 I=17
B1 3 4 V=exp(pi^i(vdd))
```

*N*+ is the positive node, and *N*- is the negative node. The values of the **V** and **I** parameters determine the voltages and currents across and through the device, respectively. If **I** is given then the device is a current source, and if **V** is given the device is a voltage source. One and only one of these parameters must be given.

The small-signal AC behavior of the non-linear source is a linear dependant source (or sources) with a proportionality constant equal to the derivitive (or derivitives) of the source at the DC operati

The expressions given for **V** and **I** may be any function of voltages and currents through voltage sources in the system. The following functions of real variables are defined:

| | | | |
|---|---|---|---|
| abs | asinh | cosh | sin |
| acos | atan | exp | sinh |
| acosh | atanh | ln | sqrt |
| asin | cos | log | tan |

The following operations are defined:

\+ - * / ^ unary -

If the argument of log, ln, or sqrt becomes less than zero, the absolute value of the argument is used. If a divisor becomes zero or the argument of log or ln becomes zero, an error will result. Other problems may occur when the argument for a function in a partial derivitive enters a region where that function is undefined.

To get time into the expression you can integrate the current from a constant current source with a capacitor and use the resulting voltage (don't forget to set the initial voltage across the capacitor). Non-linear capacitors, resistors, and inductors may be synthisized with the non-linear dependant source. Non-linear resistors are obvious. Non-linear capacitors and inductors are implemented with their linear counterparts by a change of variables implemented with the non-linear dependant source. The following subcircuit will implement a non-linear capacitor:

```
* Bx: calculate f(input voltage)
Bx   1    0    v = f(v(pos,neg))
* Cx: linear capacitance
Cx   2    0    1
* Vx: Ammeter to measure current into the capacitor
Vx   2    1    DC 0Volts
* Drive the current through Cx back into the circuit
Fx   pos  neg  Vx 1
```

Non-linear inductors are similar.

### 7.8. Independent Sources

**General form:**

```
VXXXXXXX N+ N- <<DC> DC/TRAN VALUE> <AC <ACMAG <ACPHASE>>>
+     <DISTOF1 <F1MAG <F1PHASE>>> <DISTOF2 <F2MAG <F2PHASE>>>
IYYYYYYY N+ N- <<DC> DC/TRAN VALUE> <AC <ACMAG <ACPHASE>>>
+     <DISTOF1 <F1MAG <F1PHASE>>> <DISTOF2 <F2MAG <F2PHASE>>>
```

**Examples:**

```
VCC 10 0 DC 6
VIN 13 2 0.001 AC 1 SIN(0 1 1MEG)
ISRC 23 21 AC 0.333 45.0 SFFM(0 1 10K 5 1K)
VMEAS 12 9
VCARRIER 1 0 DISTOF1 0.1 -90.0
VMODULATOR 2 0 DISTOF2 0.01
IIN1 1 5 AC 1 DISTOF1 DISTOF2 0.001
```

N+ and N- are the positive and negative nodes, respectively. Note that voltage sources need not be grounded. Positive current is assumed to flow from the positive node, through the source, to the negative node. A current source of positive value forces current to flow out of the N+ node, through the source, and into the N- node. Voltage sources, in addition to being used for circuit excitation, are the 'ammeters' for SPICE, that is, zero valued voltage sources may be inserted into the circuit for the purpose of measuring current. They of course have no effect on circuit operation since they represent short-circuits.

DC/TRAN is the dc and transient analysis value of the source. If the source value is zero both for dc and transient analyses, this value may be omitted. If the source value is time-invariant (e.g., a power supply), then the value may optionally be preceded by the letters DC.

ACMAG is the ac magnitude and ACPHASE is the ac phase. The source is set to this value in the ac analysis. If ACMAG is omitted following the keyword AC, a value of unity is assumed. If ACPHASE is omitted, a value of zero is assumed. If the source is not an ac small-signal input, the keyword AC and the ac values are omitted.

DISTOF1 and DISTOF2 are the keywords that specify that the independent source has distortion inputs at the frequencies F1 and F2 respectively (see the description of the .DISTO control line). The keywords may be followed by an optional magnitude and phase. The default values of the magnitude and phase are 1.0 and 0.0 respectively.

Any independent source can be assigned a time-dependent value for transient analysis. If a source is assigned a time-dependent value, the time-zero value is used for dc analysis. There are five independent source functions: pulse, exponential, sinusoidal, piece-wise linear, and single-frequency FM. If parameters other than source values are omitted or set to zero, the default values shown are assumed. (TSTEP is the printing increment and TSTOP is the final time (see the .TRAN control line for explanation)).

### 7.8.1. Pulse

**General form:**

```
PULSE(V1 V2 TD TR TF PW PER)
```

**Examples:**

```
VIN 3 0 PULSE(-1 1 2NS 2NS 2NS 50NS 100NS)
```

| parameter | default value | units |
|---|---|---|
| V1 (initial value) | | Volts or Amps |
| V2 (pulsed value) | | Volts or Amps |
| TD (delay time) | 0.0 | seconds |
| TR (rise time) | TSTEP | seconds |
| TF (fall time) | TSTEP | seconds |
| PW (pulse width) | TSTOP | seconds |
| PER(period) | TSTOP | seconds |

A single pulse so specified is described by the following table:

| time | value |
|---|---|
| 0 | V1 |
| TD | V1 |
| TD+TR | V2 |
| TD+TR+PW | V2 |
| TD+TR+PW+TF | V1 |
| TSTOP | V1 |

Intermediate points are determined by linear interpolation.

### 7.8.2. Sinusoidal

**General form:**

```
SIN(VO VA FREQ TD THETA)
```

**Examples:**

```
VIN 3 0 SIN(0 1 100MEG 1NS 1E10)
```

| parameters | default value | units |
|---|---|---|
| VO (offset) | | Volts or Amps |
| VA (amplitude) | | Volts or Amps |
| FREQ (frequency) | 1/TSTOP | Hz |
| TD (delay) | 0.0 | seconds |
| THETA (damping factor) | 0.0 | 1/seconds |

The shape of the waveform is described by the following table:

| time | value |
|---|---|
| 0 to TD | VO |
| TD to TSTOP | $VO + VA\, e^{-(t - TD)THETA} \sin(2\,\pi\, FREQ\, (t + TD))$ |

### 7.8.3. Exponential

**General Form:**

```
EXP(V1 V2 TD1 TAU1 TD2 TAU2)
```

**Examples:**

```
VIN 3 0 EXP(-4 -1 2NS 30NS 60NS 40NS)
```

| parameter | default value | units |
|---|---|---|
| V1 (initial value) | | Volts or Amps |
| V2 (pulsed value) | | Volts or Amps |
| TD1 (rise delay time) | 0.0 | seconds |
| TAU1 (rise time constant) | TSTEP | seconds |
| TD2 (fall delay time) | TD1+TSTEP | seconds |
| TAU2 (fall time constant) | TSTEP | seconds |

The shape of the waveform is described by the following table:

| time | value |
|---|---|
| 0 to TD1 | V1 |
| TD1 to TD2 | $V1 + (V2 - V1)\left(1 - e^{\frac{-(t - TD1)}{TAU1}}\right)$ |
| TD2 to TSTOP | $V1 + (V2 - V1)\left(-e^{\frac{-(t - TD1)}{TAU1}}\right) + (V1 - V2)\left(1 - e^{\frac{-(t - TD2)}{TAU2}}\right)$ |

### 7.8.4. Piece-Wise Linear

**General Form:**

```
PWL(T1 V1 <T2 V2 T3 V3 T4 V4 ...>)
```

**Examples:**

```
VCLOCK 7 5 PWL(0 -7 10NS -7 11NS -3 17NS -3 18NS -7 50NS -7)
```

Each pair of values (Ti, Vi) specifies that the value of the source is Vi (in Volts or Amps) at time=Ti. The value of the source at intermediate values of time is determined by using linear interpolation on the input values.

### 7.8.5. Single-Frequency FM

**General Form:**

```
SFFM(VO VA FC MDI FS)
```

**Examples:**

```
V1 12 0 SFFM(0 1M 20K 5 1K)
```

| parameter | default value | units |
|---|---|---|
| VO (offset) | | Volts or Amps |
| VA (amplitude) | | Volts or Amps |
| FC (carrier frequency) | 1/TSTOP | Hz |
| MDI (modulation index) | | |
| FS (signal frequency) | 1/TSTOP | Hz |

The shape of the waveform is described by the following equation:

$$V(t)=V_O + V_A \sin\left( 2 \pi FC\ t + MDI \sin(2 \pi FS\ t)\right)$$

## 7.9. Switches

**General form:**

```
SXXXXXXX N+ N- NC+ NC- MODEL <ON><OFF>
WYYYYYYY N+ N- VNAM MODEL <ON><OFF>
```

**Examples:**

```
s1 1 2 3 4 switch1 ON
s2 5 6 3 0 sm2 off
Switch1 1 2 10 0 smodel1
w1 1 2 vclock switchmod1
W2 3 0 vramp sm1 ON
wreset 5 6 vclck lossyswitch OFF
```

Nodes 1 and 2 are the nodes between which the switch terminals are connected. The model name is mandatory while the initial conditions are optional. For the voltage controlled switch, nodes 3 and 4 are the positive and negative controlling nodes respectively. For the current controlled switch, the controlling current is that through the specified voltage source. The direction of positive controlling current flow is from the positive node, through the source, to the negative node.

## 8. SEMICONDUCTOR DEVICES

The elements described to this point typically require only a few parameter values. However, the models for the semiconductor devices that are included in the SPICE program require many parameter values. Often, many devices in a circuit are defined by the same set of device model parameters. For these reasons, a set of device model parameters is defined on a separate .MODEL line and assigned a unique model name. The device element lines in SPICE then refer to the model name. This scheme alleviates the need to specify all of the model parameters for each device element.

Each device element line contains the device name, the nodes to which the device is connected, and the device model name. In addition, other optional parameters may be specified for some devices: geometric factors and an initial condition.

The area factor used on the diode, BJT, JFET, and MESFET devices determines the number of equivalent parallel devices of a specified model. The affected parameters are marked with an asterisk under the heading 'area' in the model descriptions below. Several geometric factors associated with the channel and the drain and source diffusions can be specified on the MOSFET device line.

Two different forms of initial conditions may be specified for some devices. The first form is included to improve the dc convergence for circuits that contain more than one stable state. If a device is specified OFF, the dc operating point is determined with the terminal voltages for that device set to zero. After convergence is obtained, the program continues to iterate to obtain the exact value for the terminal voltages. If a circuit has more than one dc stable state, the OFF option can be used to force the solution to correspond to a desired state. If a device is specified OFF when in reality the device is conducting, the program still obtains the correct solution (assuming the solutions converge) but more iterations are required since the program must independently converge to two separate solutions. The .NODESET control line serves a similar purpose as the OFF option. The .NODESET option is easier to apply and is the preferred means to aid convergence.

The second form of initial conditions are specified for use with the transient analysis. These are true 'initial conditions' as opposed to the convergence aids above. See the description of the .IC control line and the .TRAN control line for a detailed explanation of initial conditions.

### 8.1. Semiconductor Resistors

**General form:**

```
RXXXXXXX N1 N2 <VALUE> <MNAME> <L=LENGTH> <W=WIDTH> <TEMP=T>
```

**Examples:**

```
RLOAD 2 10 10K
RMOD 3 7 RMODEL L=10u W=1u
```

This is the more general form of the resistor presented in section 6.1, and allows the modeling of temperature effects and for the calculation of the actual resistance value from strictly geometric information and the specifications of the process. If VALUE is specified, it overrides the geometric information

and defines the resistance. If MNAME is specified, then the resistance may be calculated from the process information in the model MNAME and the given LENGTH and WIDTH. If VALUE is not specified, then MNAME and LENGTH **must** be specified. If WIDTH is not specified, then it is taken from the default width given in the model. The (optional) TEMP value is the temperature at which this device is to operate, and overrides the temperature specification on the .OPTION control line.

### 8.2. Semiconductor Capacitors

**General form:**

```
CXXXXXXX N1 N2 <VALUE> <MNAME> <L=LENGTH> <W=WIDTH> <IC=VAL>
```

**Examples:**

```
CLOAD 2 10 10P
CMOD 3 7 CMODEL L=10u W=1u
```

This is the more general form of the Capacitor presented in section 6.2, and allows for the calculation of the actual capacitance value from strictly geometric information and the specifications of the process. If VALUE is specified, it defines the capacitance. If MNAME is specified, then the capacitance is calculated from the process information in the model MNAME and the given LENGTH and WIDTH. If VALUE is not specified, then MNAME and LENGTH **must** be specified. If WIDTH is not specified, then it is taken from the default width given in the model. Either VALUE or MNAME, LENGTH, and WIDTH may be specified, but not both sets.

### 8.3. Uniform Distributed RC Lines (Lossy)

**General form:**

```
UXXXXXXX N1 N2 N3 MNAME L=LEN <N=LUMPS>
```

**Examples:**

```
U1 1 2 0 URCMOD L=50U
URC2 1 12 2 UMODL l=1MIL N=6
```

N1 and N2 are the two element nodes the RC line connects, while N3 is the node to which the capacitances are connected. MNAME is the model name, LEN is the length of the RC line in meters. LUMPS, if specified, is the number of lumped segments to use in modeling the RC line (see the model description for the action taken if this parameter is omitted).

### 8.4. Junction Diodes

**General form:**

```
DXXXXXXX N+ N- MNAME <AREA> <OFF> <IC=VD> <TEMP=T>
```

**Examples:**

```
DBRIDGE 2 10 DIODE1
DCLMP 3 7 DMOD 3.0 IC=0.2
```

N+ and N- are the positive and negative nodes, respectively. MNAME is the model name, AREA is the area factor, and OFF indicates an (optional) starting condition on the device for dc analysis. If the area factor is omitted, a value of 1.0 is assumed. The (optional) initial condition specification using IC=VD is intended for use with the UIC option on the .TRAN control line, when a transient analysis is desired starting from other than the quiescent operating point. The (optional) TEMP value is the temperature at which this device is to operate, and overrides the temperature specification on the .OPTION control line.

### 8.5. Bipolar Junction Transistors (BJT's)

**General form:**

```
QXXXXXXX NC NB NE <NS> MNAME <AREA> <OFF> <IC=VBE, VCE> <TEMP=T>
```

**Examples:**

```
Q23 10 24 13 QMOD IC=0.6, 5.0
Q50A 11 26 4 20 MOD1
```

NC, NB, and NE are the collector, base, and emitter nodes, respectively. NS is the (optional) substrate node. If unspecified, ground is used. MNAME is the model name, AREA is the area factor, and OFF indicates an (optional) initial condition on the device for the dc analysis. If the area factor is omitted, a value of 1.0 is assumed. The (optional) initial condition specification using IC=VBE, VCE is intended for use with the UIC option on the .TRAN control line, when a transient analysis is desired starting from other than the quiescent operating point. See the .IC control line description for a better way to set transient initial conditions. The (optional) TEMP value is the temperature at which this device is to operate, and overrides the temperature specification on the .OPTION control line.

### 8.6. Junction Field-Effect Transistors (JFET's)

**General form:**

```
JXXXXXXX ND NG NS MNAME <AREA> <OFF> <IC=VDS, VGS> <TEMP=T>
```

**Examples:**

```
J1 7 2 3 JM1 OFF
```

ND, NG, and NS are the drain, gate, and source nodes, respectively. MNAME is the model name, AREA is the area factor, and OFF indicates an (optional) initial condition on the device for dc analysis. If the area factor is omitted, a value of 1.0 is assumed. The (optional) initial condition specification, using IC=VDS, VGS is intended for use with the UIC option on the .TRAN control line, when a transient analysis is desired starting from other than the quiescent operating point. See the .IC control line for a better way to set initial conditions. The (optional) TEMP value is the temperature at which this device is to operate, and overrides the temperature specification on the .OPTION control line.

### 8.7. MOSFET's

**General form:**

```
MXXXXXXX ND NG NS NB MNAME <L=VAL> <W=VAL> <AD=VAL> <AS=VAL>
+ <PD=VAL> <PS=VAL> <NRD=VAL> <NRS=VAL> <OFF>
+ <IC=VDS, VGS, VBS> <TEMP=T>
```

**Examples:**

```
M1 24 2 0 20 TYPE1
M31 2 17 6 10 MODM L=5U W=2U
M1 2 9 3 0 MOD1 L=10U W=5U AD=100P AS=100P PD=40U PS=40U
```

ND, NG, NS, and NB are the drain, gate, source, and bulk (substrate) nodes, respectively. MNAME is the model name. L and W are the channel length and width, in meters. AD and AS are the areas of the drain and source diffusions, in meters$^2$. Note that the suffix U specifies microns (1e-6 m) and P sq-microns (1e-12 m$^2$). If any of L, W, AD, or AS are not specified, default values are used. The use of defaults simplifies input deck preparation, as well as the editing required if device geometries are to be changed. PD and PS are the perimeters of the drain and source junctions, in meters. NRD and NRS designate the equivalent number of squares of the drain and source diffusions; these values multiply the sheet resistance RSH specified on the .MODEL control line for an accurate representation of the parasitic series drain and source resistance of each transistor. PD and PS default to 0.0 while NRD and NRS to 1.0. OFF indicates an (optional) initial condition on the device for dc analysis. The (optional) initial condition specification using IC=VDS, VGS, VBS is intended for use with the UIC option on the .TRAN control line, when a transient analysis is desired starting from other than the quiescent operating point. See the .IC control line for a better and more convenient way to specify transient initial conditions. The (optional) TEMP value is the temperature at which this device is to operate, and overrides the temperature specification on the .OPTION control line. The temperature specification is ONLY valid for level 1, 2, and 3 MOSFET's, not for level 4

or BSIM devices.

### 8.8. MESFETs

**General form:**

```
ZXXXXXXX ND NG NS MNAME <AREA> <OFF> <IC=VDS, VGS>
```

**Examples:**

```
Z1 7 2 3 ZM1 OFF
```

ND, NG, and NS are the drain, gate, and source nodes, respectively. MNAME is the model name, AREA is the area factor, and OFF indicates an (optional) initial condition on the device for dc analysis. If the area factor is omitted, a value of 1.0 is assumed. The (optional) initial condition specification, using IC=VDS, VGS is intended for use with the UIC option on the .TRAN control line, when a transient analysis is desired starting from other than the quiescent operating point. See the .IC control line for a better way to set initial conditions.

## 9. DEVICE MODELS

**General form:**

```
.MODEL MNAME TYPE(PNAME1=PVAL1 PNAME2=PVAL2 ... )
```

**Examples:**

```
.MODEL MOD1 NPN (BF=50 IS=1E-13 VBF=50)
```

The .MODEL line specifies a set of model parameters that are used by one or more devices. MNAME is the model name, and type is one of the following fifteen types:

| | |
|---|---|
| R | Resistor model |
| C | Capacitor model |
| URC | Uniform distributed RC model |
| D | Diode model |
| LTRA | Lossy transmission line model |
| NPN | NPN BJT model |
| PNP | PNP BJT model |
| NJF | N-channel JFET model |
| PJF | P-channel JFET model |
| NMOS | N-channel MOSFET model |
| PMOS | P-channel MOSFET model |
| NMF | N-channel MESFET model |
| PMF | P-channel MESFET model |
| SW | Voltage controlled switch |
| CSW | Current controlled switch |

Parameter values are defined by appending the parameter name, as given below for each model type, followed by an equal sign and the parameter value. Model parameters that are not given a value are assigned the default values given below for each model type.

### 9.1. Resistor Model

The resistor model consists of process-related device data that allow the resistance to be calculated from geometric information and to be corrected for temperature. The parameters available are:

| name | parameter | units | default | example |
|---|---|---|---|---|
| TC1 | first order temperature coeff. | Ω/°C | 0.0 | - |
| TC2 | second order temperature coeff. | Ω/°C$^2$ | 0.0 | - |
| RSH | sheet resistance | Ω/□ | - | 50 |
| DEFW | default width | meters | 1e-6 | 2e-6 |
| NARROW | narrowing due to side etching | meters | 0.0 | 1e-7 |
| TNOM | parameter measurement temperature | °C | 27 | 50 |

The sheet resistance is used with the narrowing parameter and L and W from the resistor device to determine the nominal resistance by the formula

$$R = RSH\frac{L - NARROW}{W - NARROW}$$

DEFW is used to supply a default value for W if one is not specified for the device. If either RSH or L is not specified, then the standard default resistance value of 1k Ω is used. TNOM is used to override the circuit-wide value given on the .OPTIONS control line where the parameters of this model have been measured at a different temperature. After the nominal resistance is calculated, it is adjusted for temperature by the formula:

$$R(T) = R(T_0)\,[1 + TC1\,(T - T_0) + TC2\,(T - T_0)^2]$$

### 9.2. Capacitor Model

The capacitor model contains process information that may be used to compute the capacitance from strictly geometric information.

| name | parameter | units | default | example |
|---|---|---|---|---|
| CJ | junction bottom capacitance | F/meters$^2$ | - | 5e-5 |
| CJSW | junction sidewall capacitance | F/meters | - | 2e-11 |
| DEFW | default device width | meters | 1e-6 | 2e-6 |
| NARROW | narrowing due to side etching | meters | 0.0 | 1e-7 |

The capacitor has a capacitance computed as

CAP = CJ (LENGTH − NARROW) (WIDTH − NARROW) + 2 CJSW (LENGTH + WIDTH − 2 NARROW)

### 9.3. Uniform Distributed RC Model

The URC model is derived from a model proposed by L. Gertzberrg in 1974. The model is accomplished by a subcircuit type expansion of the URC line into a network of lumped RC segments with internally generated nodes. The RC segments are in a geometric progression, increasing toward the middle of the URC line, with K as a proportionality constant. The number of lumped segments used, if not specified for the URC line device, is determined by the following formula:

$$N = \frac{\log\left[ F_{max} \frac{R}{L} \frac{C}{L} 2 \pi L^2 \left( \frac{(K-1)}{K} \right)^2 \right]}{\log K}$$

The URC line is made up strictly of resistor and capacitor segments unless the ISPERL parameter is given a non-zero value, in which case the capacitors are replaced with reverse biased diodes with a zero-bias junction capacitance equivalent to the capacitance replaced, and with a saturation current of ISPERL amps per meter of transmission line and an optional series resistance equivalent to RSPERL ohms per meter.

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 1 | K | Propagation Constant | - | 2.0 | 1.2 | - |
| 2 | FMAX | Maximum Frequency of interest | Hz | 1.0G | 6.5Meg | - |
| 3 | RPERL | Resistance per unit length | Ω/m | 1000 | 10 | - |
| 4 | CPERL | Capacitance per unit length | F/m | 1.0e-15 | 1pF | - |
| 5 | ISPERL | Saturation Current per unit length | A/m | 0 | - | - |
| 6 | RSPERL | Diode Resistance per unit length | Ω/m | 0 | - | - |

### 9.4. Lossy Transmission Line (LTRA) Model

The uniform RLC/RC/LC/RG transmission line model (referred to as the LTRA model henceforth) models a uniform constant-parameter distributed transmission line. The RC and LC cases may also be modelled using the URC and TRA models; however, the newer LTRA model is usually faster and more accurate than the others. The operation of the LTRA model is based on the convolution of the transmission line's impulse responses with its inputs see [9].

The LTRA model takes a number of parameters, some of which must be given and some of which are optional.

| name | parameter | units/type | default | example |
|---|---|---|---|---|
| R | resistance/length | Ω/unit | 0.0 | 0.2 |
| L | inductance/length | henrys/unit | 0.0 | 9.13e-9 |
| G | conductance/length | mhos/unit | 0.0 | 0.0 |
| C | capacitance/length | farads/unit | 0.0 | 3.65e-12 |
| LEN | length of line | | no default | 1.0 |
| REL | breakpoint control | arbitrary unit | 1 | 0.5 |
| ABS | breakpoint control | | 1 | 5 |
| NOSTEPLIMIT | don't limit timestep to less than line delay | flag | not set | set |
| NOCONTROL | don't do complex timestep control | flag | not set | set |
| LININTERP | use linear interpolation | flag | not set | set |
| MIXEDINTERP | use linear when quadratic seems bad | | not set | set |
| COMPACTREL | special reltol for history compaction | flag | RELTOL | 1.0e-3 |
| COMPACTABS | special abstol for history compaction | | ABSTOL | 1.0e-9 |
| TRUNCNR | use Newton-Raphson method for timestep control | flag | not set | set |
| TRUNCDONTCUT | don't limit timestep to keep impulse-response errors low | flag | not set | set |

The following types of lines have been implemented so far: RLC (uniform transmission line with series loss only), RC (uniform RC line), LC (lossless transmission line), and RG (distributed series resistance and parallel conductance only). Any other combination will yield erroneous results and should not be tried. The length LEN of the line must be specified.

NOSTEPLIMIT is a flag that will remove the default restriction of limiting time-steps to less than the line delay in the RLC case. NOCONTROL is a flag that prevents the default limiting of the time-step based on convolution error criteria in the RLC and RC cases. This speeds up simulation but may in some cases reduce the accuracy of results. LININTERP is a flag that, when specified, will use linear interpolation instead of the default quadratic interpolation for calculating delayed signals. MIXEDINTERP is a flag that, when specified, uses a metric for judging whether qua- dratic interpolation is not applicable and if so

uses linear interpolation; otherwise it uses the default quadratic interpolation. TRUNCDONTCUT is a flag that removes the default cutting of the time-step to limit errors in the actual calculation of impulse-response related quantities. COMPACTREL and COMPACTABS are quantities that control the compaction of the past history of values stored for convolution. Larger values of these lower accuracy but usually increase simulation speed These are to be used with the TRYTOCOMPACT option, described in the .OPTIONS section. TRUNCNR is a flag that turns on the use of Newton-Raphson iterations to determine an appropriate timestep in the timestep control routines. The default is a trial and error procedure by cutting the previous timestep in half. REL and ABS are quantities that control the setting of breakpoints.

The option most worth experimenting with for increasing the speed of simulation is REL. The default value of 1 is usually safe from the point of view of accuracy but occa- sionally increases computation time. A value of greater than 2 eliminates all breakpoints and may be worth trying depend- ing on the nature of the rest of the circuit, keeping in mind that it might not be safe from the viewpoint of accu- racy. Breakpoints may usually be entirely eliminated if it is expected the circuit will not display sharp discontinui- ties. Values between 0 and 1 are usually not required but may be used for setting many breakpoints.

COMPACTREL may also be experimented with when the option TRYTOCOMPACT is specified in a .OPTIONS card. The legal range is between 0 and 1. Larger values usually decrease the accuracy of the simulation but in some cases improve speed. If TRYTOCOMPACT is not specified on a .OPTIONS card, history compaction is not attempted and accuracy is high. NOCONTROL, TRUNCDONTCUT and NOSTEPLIMIT also tend to increase speed at the expense of accuracy.

### 9.5. Switch Model

The switch model allows an almost ideal switch to be described in SPICE. The switch is not quite ideal, in that the resistance can not change from 0 to infinity, but must always have a finite positive value. By proper selection of the on and off resistances, they can be effectively zero and infinity in comparison to other circuit elements. The parameters available are:

| name | parameter | units | default | switch |
|---|---|---|---|---|
| VT | threshold voltage | Volts | 0.0 | S |
| IT | threshold current | Amps | 0.0 | W |
| VH | hysteresis voltage | Volts | 0.0 | S |
| IH | hysteresis current | Amps | 0.0 | W |
| RON | on resistance | Ω | 1.0 | both |
| ROFF | off resistance | Ω | 1/GMIN* | both |

*(See the .OPTIONS control line for a description of GMIN, its default value results is a off resistance of 1.0e+12 ohms.)

The use of an ideal element that is highly non-linear such as a switch can cause large discontinuities to occur in the circuit node voltages. A rapid change such as that associated with a switch changing state can cause numerical roundoff or tolerance problems leading to erroneous results or timestep difficulties. The user of switches can improve the situation by taking the following steps:

First of all it is wise to set ideal switch impedances only high and low enough to be negligible with respect to other circuit elements. Using switch impedances that are close to "ideal" in all cases aggravates the problem of discontinuities mentioned above. Of course, when modeling real devices such as MOSFETS, the on resistance should be adjusted to a realistic level depending on the size of the device being modeled.

If a wide range of ON to OFF resistance must be used in the switches (ROFF/RON >1e+12), then the tolerance on errors allowed during transient analysis should be decreased by using the .OPTIONS control line and specifying TRTOL to be less than the default value of 7.0. When switches are placed around capacitors, then the option CHGTOL should also be reduced. Suggested values for these two options are 1.0 and 1e-16 respectively. These changes inform SPICE3 to be more careful around the switch points so that no errors are made due to the rapid change in the circuit.

## 9.6. Diode Model

The dc characteristics of the diode are determined by the parameters IS and N. An ohmic resistance, RS, is included. Charge storage effects are modeled by a transit time, TT, and a nonlinear depletion layer capacitance which is determined by the parameters CJO, VJ, and M. The temperature dependence of the saturation current is defined by the parameters EG, the energy and XTI, the saturation current temperature exponent. The nominal temperature at which these parameters were measured is TNOM, which defaults to the circuit-wide value specified on the .OPTIONS control line. Reverse breakdown is modeled by an exponential increase in the reverse diode current and is determined by the parameters BV and IBV (both of which are positive numbers).

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 1 | IS | saturation current | A | 1.0e-14 | 1.0e-14 | * |
| 2 | RS | ohmic resistance | Ω | 0 | 10 | * |
| 3 | N | emission coefficient | - | 1 | 1.0 | |
| 4 | TT | transit-time | sec | 0 | 0.1ns | |
| 5 | CJO | zero-bias junction capacitance | F | 0 | 2pF | * |
| 6 | VJ | junction potential | V | 1 | 0.6 | |
| 7 | M | grading coefficient | - | 0.5 | 0.5 | |
| 8 | EG | activation energy | eV | 1.11 | 1.11 Si | |
| | | | | | 0.69 Sbd | |
| | | | | | 0.67 Ge | |
| 9 | XTI | saturation-current temp. exp | - | 3.0 | 3.0 jn | |
| | | | | | 2.0 Sbd | |
| 10 | KF | flicker noise coefficient | - | 0 | | |
| 11 | AF | flicker noise exponent | - | 1 | | |
| 12 | FC | coefficient for forward-bias depletion capacitance formula | - | 0.5 | | |
| 13 | BV | reverse breakdown voltage | V | infinite | 40.0 | |
| 14 | IBV | current at breakdown voltage | A | 1.0e-3 | | |
| 15 | TNOM | parameter measurement temperature | °C | 27 | 50 | |

### 9.7. BJT Models (both NPN and PNP)

The bipolar junction transistor model in SPICE is an adaptation of the integral charge control model of Gummel and Poon. This modified Gummel-Poon model extends the original model to include several effects at high bias levels. The model automatically simplifies to the simpler Ebers-Moll model when certain parameters are not specified. The parameter names used in the modified Gummel-Poon model have been chosen to be more easily understood by the program user, and to reflect better both physical and circuit design thinking.

The dc model is defined by the parameters IS, BF, NF, ISE, IKF, and NE which determine the forward current gain characteristics, IS, BR, NR, ISC, IKR, and NC which determine the reverse current gain characteristics, and VAF and VAR which determine the output conductance for forward and reverse regions. Three ohmic resistances RB, RC, and RE are included, where RB can be high current dependent. Base charge storage is modeled by forward and reverse transit times, TF and TR, the forward transit time TF being bias dependent if desired, and nonlinear depletion layer capacitances which are determined by CJE, VJE, and MJE for the B-E junction , CJC, VJC, and MJC for the B-C junction and CJS, VJS, and MJS for the C-S (Collector-Substrate) junction. The temperature dependence of the saturation current, IS, is determined by the energy-gap, EG, and the saturation current temperature exponent, XTI. Additionally base current temperature dependence is modeled by the beta temperature exponent XTB in the new model.

The values specified are assumed to have been measured at the temperature TNOM, which can be specified on the .OPTIONS control line or overridden by a specification on the .MODEL line.

The BJT parameters used in the modified Gummel-Poon model are listed below. The parameter names used in earlier versions of SPICE2 are still accepted.

Modified Gummel-Poon BJT Parameters.

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 1 | IS | transport saturation current | A | 1.0e-16 | 1.0e-15 | * |
| 2 | BF | ideal maximum forward beta | - | 100 | 100 | |
| 3 | NF | forward current emission coefficient | - | 1.0 | 1 | |
| 4 | VAF | forward Early voltage | V | infinite | 200 | |
| 5 | IKF | corner for forward beta | | | | |
| | | high current roll-off | A | infinite | 0.01 | * |
| 6 | ISE | B-E leakage saturation current | A | 0 | 1.0e-13 | * |
| 7 | NE | B-E leakage emission coefficient | - | 1.5 | 2 | |
| 8 | BR | ideal maximum reverse beta | - | 1 | 0.1 | |
| 9 | NR | reverse current emission coefficient | - | 1 | 1 | |
| 10 | VAR | reverse Early voltage | V | infinite | 200 | |
| 11 | IKR | corner for reverse beta | | | | |
| | | high current roll-off | A | infinite | 0.01 | * |
| 12 | ISC | B-C leakage saturation current | A | 0 | 1.0e-13 | * |
| 13 | NC | B-C leakage emission coefficient | - | 2 | 1.5 | |
| 14 | RB | zero bias base resistance | Ω | 0 | 100 | * |
| 15 | IRB | current where base resistance | | | | |
| | | falls halfway to its min value | A | infinite | 0.1 | * |
| 16 | RBM | minimum base resistance | | | | |
| | | at high currents | Ω | RB | 10 | * |
| 17 | RE | emitter resistance | Ω | 0 | 1 | * |
| 18 | RC | collector resistance | Ω | 0 | 10 | * |
| 19 | CJE | B-E zero-bias depletion capacitance | F | 0 | 2pF | * |
| 20 | VJE | B-E built-in potential | V | 0.75 | 0.6 | |
| 21 | MJE | B-E junction exponential factor | - | 0.33 | 0.33 | |
| 22 | TF | ideal forward transit time | sec | 0 | 0.1ns | |
| 23 | XTF | coefficient for bias dependence of TF | - | 0 | | |
| 24 | VTF | voltage describing VBC | | | | |
| | | dependence of TF | V | infinite | | |
| 25 | ITF | high-current parameter | | | | |
| | | for effect on TF | A | 0 | | * |
| 26 | PTF | excess phase at freq=1.0/(TF*2PI) Hz | deg | 0 | | |

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 27 | CJC | B-C zero-bias depletion capacitance | F | 0 | 2pF | * |
| 28 | VJC | B-C built-in potential | V | 0.75 | 0.5 | |
| 29 | MJC | B-C junction exponential factor | - | 0.33 | 0.5 | |
| 30 | XCJC | fraction of B-C depletion capacitance connected to internal base node | - | 1 | | |
| 31 | TR | ideal reverse transit time | sec | 0 | 10ns | |
| 32 | CJS | zero-bias collector-substrate capacitance | F | 0 | 2pF | * |
| 33 | VJS | substrate junction built-in potential | V | 0.75 | | |
| 34 | MJS | substrate junction exponential factor | - | 0 | 0.5 | |
| 35 | XTB | forward and reverse beta temperature exponent | - | 0 | | |
| 36 | EG | energy gap for temperature effect on IS | eV | 1.11 | | |
| 37 | XTI | temperature exponent for effect on IS | - | 3 | | |
| 38 | KF | flicker-noise coefficient | - | 0 | | |
| 39 | AF | flicker-noise exponent | - | 1 | | |
| 40 | FC | coefficient for forward-bias depletion capacitance formula | - | 0.5 | | |
| 41 | TNOM | Parameter measurement temperature | °C | 27 | 50 | |

### 9.8. JFET Models (both N and P Channel)

The JFET model is derived from the FET model of Shichman and Hodges. The dc characteristics are defined by the parameters VTO and BETA, which determine the variation of drain current with gate voltage, LAMBDA, which determines the output conductance, and IS, the saturation current of the two gate junctions. Two ohmic resistances, RD and RS, are included. Charge storage is modeled by nonlinear depletion layer capacitances for both gate junctions which vary as the -1/2 power of junction voltage and are defined by the parameters CGS, CGD, and PB.

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 1 | VTO | threshold voltage ($V_{TO}$ | V | -2.0 | -2.0 | |
| 2 | BETA | transconductance parameter ($\beta$) | $A/V^2$ | 1.0e-4 | 1.0e-3 | * |
| 3 | LAMBDA | channel length modulation parameter ($\lambda$) | 1/V | 0 | 1.0e-4 | |
| 4 | RD | drain ohmic resistance | $\Omega$ | 0 | 100 | * |
| 5 | RS | source ohmic resistance | $\Omega$ | 0 | 100 | * |
| 6 | CGS | zero-bias G-S junction capacitance ($C_{gs}$) | F | 0 | 5pF | * |
| 7 | CGD | zero-bias G-D junction capacitance ($C_{gs}$) | F | 0 | 1pF | * |
| 8 | PB | gate junction potential | V | 1 | 0.6 | |
| 9 | IS | gate junction saturation current ($I_S$) | A | 1.0e-14 | 1.0e-14 | * |
| 10 | KF | flicker noise coefficient | - | 0 | | |
| 11 | AF | flicker noise exponent | - | 1 | | |
| 12 | FC | coefficient for forward-bias depletion capacitance formula | - | 0.5 | | |
| 13 | TNOM | parameter measurement temperature | °C | 27 | 50 | |

### 9.9. MOSFET Models (both N and P channel)

SPICE provides four MOSFET device models, which differ in the formulation of the I-V characteristic. The variable LEVEL specifies the model to be used:

| | |
|---|---|
| LEVEL=1 -> | Shichman-Hodges |
| LEVEL=2 -> | MOS2 (as described in [1]) |
| LEVEL=3 -> | MOS3, a semi-empirical model(see [1]) |
| LEVEL=4 -> | BSIM (as described in [3]) |
| LEVEL=5 -> | new BSIM (BSIM2; as described in [5]) |
| LEVEL=6 -> | MOS6 (as described in [2]) |

The dc characteristics of the level 1 through level 3 MOSFETs are defined by the device parameters VTO,

KP, LAMBDA, PHI and GAMMA. These parameters are computed by SPICE if process parameters (NSUB, TOX, ...) are given, but user-specified values always override. VTO is positive (negative) for enhancement mode and negative (positive) for depletion mode N-channel (P-channel) devices. Charge storage is modeled by three constant capacitors, CGSO, CGDO, and CGBO which represent overlap capacitances, by the nonlinear thin-oxide capacitance which is distributed among the gate, source, drain, and bulk regions, and by the nonlinear depletion-layer capacitances for both substrate junctions divided into bottom and periphery, which vary as the MJ and MJSW power of junction voltage respectively, and are determined by the parameters CBD, CBS, CJ, CJSW, MJ, MJSW and PB. Charge storage effects are modeled by the piecewise linear voltages-dependent capacitance model proposed by Meyer. The thin-oxide charge-storage effects are treated slightly different for the LEVEL=1 model. These voltage-dependent capacitances are included only if TOX is specified in the input description and they are represented using Meyer's formulation.

There is some overlap among the parameters describing the junctions, e.g. the reverse current can be input either as IS (in A) or as JS (in $A/m^2$). Whereas the first is an absolute value the second is multiplied by AD and AS to give the reverse current of the drain and source junctions respectively. This methodology has been chosen since there is no sense in relating always junction characteristics with AD and AS entered on the device line; the areas can be defaulted. The same idea applies also to the zero-bias junction capacitances CBD and CBS (in F) on one hand, and CJ (in $F/m^2$) on the other. The parasitic drain and source series resistance can be expressed as either RD and RS (in ohms) or RSH (in ohms/sq.), the latter being multiplied by the number of squares NRD and NRS input on the device line.

SPICE level 1 to level 3 and level 6 parameters.

| | name | parameter | units | default | example |
|---|---|---|---|---|---|
| 1 | LEVEL | model index | - | 1 | |
| 2 | VTO | zero-bias threshold voltage ($V_{TO}$) | V | 0.0 | 1.0 |
| 3 | KP | transconductance parameter | $A/V^2$ | 2.0e-5 | 3.1e-5 |
| 4 | GAMMA | bulk threshold parameter ($\gamma$) | $V^{1/2}$ | 0.0 | 0.37 |
| 5 | PHI | surface potential ($\phi$) | V | 0.6 | 0.65 |
| 6 | LAMBDA | channel-length modulation (MOS1 and MOS2 only) ($\lambda$) | 1/V | 0.0 | 0.02 |
| 7 | RD | drain ohmic resistance | $\Omega$ | 0.0 | 1.0 |
| 8 | RS | source ohmic resistance | $\Omega$ | 0.0 | 1.0 |
| 9 | CBD | zero-bias B-D junction capacitance | F | 0.0 | 20fF |
| 10 | CBS | zero-bias B-S junction capacitance | F | 0.0 | 20fF |
| 11 | IS | bulk junction saturation current ($I_S$) | A | 1.0e-14 | 1.0e-15 |
| 12 | PB | bulk junction potential | V | 0.8 | 0.87 |
| 13 | CGSO | gate-source overlap capacitance per meter channel width | F/m | 0.0 | 4.0e-11 |
| 14 | CGDO | gate-drain overlap capacitance | | | |

| | name | parameter | units | default | example |
|---|---|---|---|---|---|
| | | per meter channel width | F/m | 0.0 | 4.0e-11 |
| 15 | CGBO | gate-bulk overlap capacitance per meter channel length | F/m | 0.0 | 2.0e-10 |
| 16 | RSH | drain and source diffusion sheet resistance | Ω/□ | 0.0 | 10.0 |
| 17 | CJ | zero-bias bulk junction bottom cap. per sq-meter of junction area | $F/m^2$ | 0.0 | 2.0e-4 |
| 18 | MJ | bulk junction bottom grading coeff. | - | 0.5 | 0.5 |
| 19 | CJSW | zero-bias bulk junction sidewall cap. per meter of junction perimeter | F/m | 0.0 | 1.0e-9 |
| 20 | MJSW | bulk junction sidewall grading coeff. | - | 0.50(level1) 0.33(level2, 3) | |
| 21 | JS | bulk junction saturation current per sq-meter of junction area | $A/m^2$ | | 1.0e-8 |
| 22 | TOX | oxide thickness | meter | 1.0e-7 | 1.0e-7 |
| 23 | NSUB | substrate doping | $1/cm^3$ | 0.0 | 4.0e15 |
| 24 | NSS | surface state density | $1/cm^2$ | 0.0 | 1.0e10 |
| 25 | NFS | fast surface state density | $1/cm^2$ | 0.0 | 1.0e10 |
| 26 | TPG | type of gate material:<br>+1 opp. to substrate<br>-1 same as substrate<br>0 Al gate | - | 1.0 | |
| 27 | XJ | metallurgical junction depth | meter | 0.0 | 1µ |
| 28 | LD | lateral diffusion | meter | 0.0 | 0.8µ |
| 29 | UO | surface mobility | $cm^2/Vs$ | 600 | 700 |
| 30 | UCRIT | critical field for mobility degradation (MOS2 only) | V/cm | 1.0e4 | 1.0e4 |
| 31 | UEXP | critical field exponent in mobility degradation (MOS2 only) | - | 0.0 | 0.1 |
| 32 | UTRA | transverse field coeff (mobility) (deleted for MOS2) | - | 0.0 | 0.3 |
| 33 | VMAX | maximum drift velocity of carriers | m/s | 0.0 | 5.0e4 |
| 34 | NEFF | total channel charge (fixed and mobile) coefficient (MOS2 only) | - | 1.0 | 5.0 |
| 35 | KF | flicker noise coefficient | - | 0.0 | 1.0e-26 |
| 36 | AF | flicker noise exponent | - | 1.0 | 1.2 |
| 37 | FC | coefficient for forward-bias depletion capacitance formula | - | 0.5 | |
| 38 | DELTA | width effect on threshold voltage (MOS2 and MOS3) | - | 0.0 | 1.0 |

| | name | parameter | units | default | example |
|---|---|---|---|---|---|
| 39 | THETA | mobility modulation (MOS3 only) | 1/V | 0.0 | 0.1 |
| 40 | ETA | static feedback (MOS3 only) | - | 0.0 | 1.0 |
| 41 | KAPPA | saturation field factor (MOS3 only) | - | 0.2 | 0.5 |
| 42 | TNOM | parameter measurement temperature | °C | 27 | 50 |

The level 4 parameters are all values obtained from process characterization, and can be generated automatically. J. Pierret [4] describes a means of generating a 'process' file, and the program Proc2Mod provided with SPICE3 converts this file into a sequence of .MODEL lines suitable for inclusion in a SPICE deck. Parameters marked below with an * in the l/w column also have corresponding parameters with a length and width dependency. For example, VFB is the basic parameter with units of Volts, and LVFB and WVFB also exist and have units of Volt-µmeter The formula

$$P = P_0 + \frac{P_L}{L_{effective}} + \frac{P_W}{W_{effective}}$$

is used to evaluate the parameter for the actual device specified with

$$L_{effective} = L_{input} - DL$$

and

$$W_{effective} = W_{input} - DW$$

Note that unlike the other models in SPICE, the BSIM model is designed for use with a process characterization system that provides all the parameters, thus there are no defaults for the parameters, and leaving one out is considered an error. For an example set of parameters and the format of a process file, see the SPICE2 implementation notes[3].

SPICE BSIM (level 4) parameters.

| name | parameter | units | l/w |
|---|---|---|---|
| VFB | flat-band voltage | V | * |
| PHI | surface inversion potential | V | * |
| K1 | body effect coefficient | $V^{1/2}$ | * |
| K2 | drain/source depletion charge-sharing coefficient | - | * |
| ETA | zero-bias drain-induced barrier-lowering coefficient | - | * |
| MUZ | zero-bias mobility | $cm^2/V–s$ | |
| DL | shortening of channel | µm | |
| DW | narrowing of channel | µm | |
| U0 | zero-bias transverse-field mobility degradation coefficient | $V^{-1}$ | * |
| U1 | zero-bias velocity saturation coefficient | µm/V | * |

| name | parameter | units | l/w |
|---|---|---|---|
| X2MZ | sens. of mobility to substrate bias at $v_{ds}$=0 | $cm^2/V^2–s$ | * |
| X2E | sens. of drain-induced barrier lowering effect to substrate bias | $V^{-1}$ | * |
| X3E | sens. of drain-induced barrier lowering effect to drain bias at $V_{ds}=V_{dd}$ | $V^{-1}$ | * |
| X2U0 | sens. of transverse field mobility degradation effect to substrate bias | $V^{-2}$ | * |
| X2U1 | sens. of velocity saturation effect to substrate bias | $\mu mV^{-2}$ | * |
| MUS | mobility at zero substrate bias and at $V_{ds}=V_{dd}$ | $cm^2/V^2–s$ | |
| X2MS | sens. of mobility to substrate bias at $V_{ds}=V_{dd}$ | $cm^2/V^2–s$ | * |
| X3MS | sens. of mobility to drain bias at $V_{ds}=V_{dd}$ | $cm^2/V^2–s$ | * |
| X3U1 | sens. of velocity saturation effect on drain bias at $V_{ds}=V_{dd}$ | $\mu mV^{-2}$ | * |
| TOX | gate oxide thickness | µm | |
| TEMP | temperature at which parameters were measured | °C | |
| VDD | measurement bias range | V | |
| CGDO | gate-drain overlap capacitance per meter channel width | F/m | |
| CGSO | gate-source overlap capacitance per meter channel width | F/m | |
| CGBO | gate-bulk overlap capacitance per meter channel length | F/m | |
| XPART | gate-oxide capacitance-charge model flag | - | |
| N0 | zero-bias subthreshold slope coefficient | - | * |
| NB | sens. of subthreshold slope to substrate bias | - | * |
| ND | sens. of subthreshold slope to drain bias | - | * |
| RSH | drain and source diffusion sheet resistance | Ω/□ | |
| JS | source drain junction current density | $A/m^2$ | |
| PB | built in potential of source drain junction | V | |
| MJ | Grading coefficient of source drain junction | - | |
| PBSW | built in potential of source, drain juntion sidewall | V | |
| MJSW | grading coefficient of source drain junction sidewall | - | |
| CJ | Source drain junction capacitance per unit area | $F/m^2$ | |
| CJSW | source drain junction sidewall capacitance per unit length | F/m | |
| WDF | source drain junction default width | m | |
| DELL | Source drain junction length reduction | m | |

XPART = 0 selects a 40/60 drain/source charge partition in saturation, while XPART=1 selects a 0/100 drain/source charge partition.

### 9.10. MESFET Models (both N and P Channel)

The MESFET model is derived from the GaAs FET model of Statz et al. as described in [6]. The dc characteristics are defined by the parameters VTO, B, and BETA, which determine the variation of drain current with gate voltage, ALPHA, which determines saturation voltage, and LAMBDA, which determines the output conductance. The formula are given by:

$$I_d = \frac{\beta\,(V_{gs}-V_T)^2}{1+b(V_{gs}-V_T)}\left[1-\left[1-\alpha\frac{V_{ds}}{3}\right]^3\right](1+\lambda\,V_{ds}) \qquad \text{for } 0 < V_{ds} < \frac{3}{\alpha}$$

$$I_d = \frac{\beta\,(V_{gs}-V_T)^2}{1+b(V_{gs}-V_T)}(1+\lambda\,V_{ds}) \qquad \text{for } V_{ds} > \frac{3}{\alpha}$$

Two ohmic resistances, RD and RS, are included. Charge storage is modeled by total gate charge as a function of gate-drain and gate-source voltages and is defined by the parameters CGS, CGD, and PB.

| | name | parameter | units | default | example | area |
|---|---|---|---|---|---|---|
| 1 | VTO | pinch-off voltage | V | -2.0 | -2.0 | |
| 2 | BETA | transconductance parameter | $A/V^2$ | 1.0e-4 | 1.0e-3 | * |
| 3 | B | doping tail extending parameter | 1/V | 0.3 | 0.3 | * |
| 4 | ALPHA | saturation voltage parameter | 1/V | 2 | 2 | * |
| 5 | LAMBDA | channel length modulation parameter | 1/V | 0 | 1.0e-4 | |
| 6 | RD | drain ohmic resistance | Ω | 0 | 100 | * |
| 7 | RS | source ohmic resistance | Ω | 0 | 100 | * |
| 8 | CGS | zero-bias G-S junction capacitance | F | 0 | 5pF | * |
| 9 | CGD | zero-bias G-D junction capacitance | F | 0 | 1pF | * |
| 10 | PB | gate junction potential | V | 1 | 0.6 | |
| 11 | KF | flicker noise coefficient | - | 0 | | |
| 12 | AF | flicker noise exponent | - | 1 | | |
| 13 | FC | coefficient for forward-bias depletion capacitance formula | - | 0.5 | | |

## 10. SUBCIRCUITS

A subcircuit that consists of SPICE elements can be defined and referenced in a fashion similar to device models. The subcircuit is defined in the input deck by a grouping of element lines; the program then automatically inserts the group of elements wherever the subcircuit is referenced. There is no limit on the size or complexity of subcircuits, and subcircuits may contain other subcircuits. An example of subcircuit usage is given in Appendix A.

### 10.1. .SUBCKT Line

**General form:**

```
.SUBCKT subnam N1 <N2 N3 ...>
```

**Examples:**

```
.SUBCKT OPAMP 1 2 3 4
```

A circuit definition is begun with a .SUBCKT line. SUBNAM is the subcircuit name, and N1, N2, ... are the external nodes, which cannot be zero. The group of element lines which immediately follow the .SUBCKT line define the subcircuit. The last line in a subcircuit definition is the .ENDS line (see below). Control lines may not appear within a subcircuit definition; however, subcircuit definitions may contain anything else, including other subcircuit definitions, device models, and subcircuit calls (see below). Note that any device models or subcircuit definitions included as part of a subcircuit definition are strictly local (i.e., such models and definitions are not known outside the subcircuit definition). Also, any element nodes not included on the .SUBCKT line are strictly local, with the exception of 0 (ground) which is always global.

### 10.2. .ENDS Line

**General form:**

```
.ENDS <SUBNAM>
```

**Examples:**

```
.ENDS OPAMP
```

This line must be the last one for any subcircuit definition. The subcircuit name, if included, indicates which subcircuit definition is being terminated; if omitted, all subcircuits being defined are terminated. The name is needed only when nested subcircuit definitions are being made.

### 10.3. Subcircuit Calls

**General form:**

```
XYYYYYYY N1 <N2 N3 ...> SUBNAM
```

**Examples:**

```
X1 2 4 17 3 1 MULTI
```

Subcircuits are used in SPICE by specifying pseudo-elements beginning with the letter X, followed by the circuit nodes to be used in expanding the subcircuit.

## 11. CONTROL LINES

The following control lines are for specifying analyses within the circuit description file. Parallel commands exist for each analysis line in the interactive command interpretor (detailed in the following section).

### 11.1. .OPTIONS Line

**General form:**

```
.OPTIONS OPT1 OPT2 ... (or OPT=OPTVAL ...)
```

**Examples:**

```
.OPTIONS RELTOL=.005 TRTOL=8
```

This line allows the user to reset program control and user options for specific simulation purposes. Additional options for Nutmeg may be specified as well and take effect when Nutmeg reads the input deck. Options specified to Nutmeg via the 'set' command are also passed on to SPICE3 as if specified on a .OPTIONS line. See the following section on the interactive command interpretor for the parameters which may be set with a .OPTIONS line and the format of the 'set' command. Any combination of the following options may be included, in any order. 'x' (below) represents some positive number.

| option | effect |
|---|---|
| GMIN=x | resets the value of GMIN, the minimum conductance allowed by the program. The default value is 1.0e-12. |
| RELTOL=x | resets the relative error tolerance of the program. The default value is 0.001 (0.1 percent). |
| ABSTOL=x | resets the absolute current error tolerance of the program. The default value is 1 picoamp. |
| VNTOL=x | resets the absolute voltage error tolerance of the program. The default value is 1 microvolt. |
| TRTOL=x | resets the transient error tolerance. The default value is 7.0. This parameter is an estimate of the factor by which SPICE overestimates the actual truncation error. |
| CHGTOL=x | resets the charge tolerance of the program. The default value is 1.0e-14. |
| PIVTOL=x | resets the absolute minimum value for a matrix entry to be accepted as a pivot. The default value is 1.0e-13. |

| option | effect |
|---|---|
| PIVREL=x | resets the relative ratio between the largest column entry and an acceptable pivot value. The default value is 1.0e-3. In the numerical pivoting algorithm the allowed minimum pivot value is determined by EPSREL=AMAX1(PIVREL*MAXVAL, PIVTOL) where MAXVAL is the maximum element in the column where a pivot is sought (partial pivoting). |
| TNOM=x | resets the nominal temperature at which device parameters are measured. The default value is 27 deg C (300 deg K). TNOM can be overridden by a specification on any temperature dependent device model. |
| TEMP=x | Resets the operating temperature of the circuit. The default value is 27 deg C (300 deg K). TEMP can be overridden by a temperature specification on any temperature dependent instance. |
| ITL1=x | resets the dc iteration limit. The default is 100. |
| ITL2=x | resets the dc transfer curve iteration limit. The default is 50. |
| ITL3=x | resets the lower transient analysis iteration limit. the default value is 4. (Note: not implemented in Spice3). |
| ITL4=x | resets the transient analysis timepoint iteration limit. the default is 10. |
| ITL5=x | resets the transient analysis total iteration limit. the default is 5000. Set ITL5=0 to omit this test. (Note: not implemented in Spice3). |
| DEFL=x | resets the value for MOS channel length; the default is 100.0 micrometer. |
| DEFW=x | resets the value for MOS channel width; the default is 100.0 micrometer. |
| DEFAD=x | resets the value for MOS drain diffusion area; the default is 0.0. |
| DEFAS=x | resets the value for MOS source diffusion area; the default is 0.0. |

| option | effect |
|---|---|
| TRYTOCOMPACT | Applicable only to the LTRA model. When specified, the simulator tries to condense LTRA transmission lines' past history of input voltages and currents. |
| METHOD=name | sets the numerical integration method used by SPICE. Possible names are "Gear" or "trapezoidal" (or just "trap"). The default is trapezoidal. |

### 11.2. .OP Line

**General form:**

```
.OP
```

The inclusion of this line in an input deck directs SPICE to determine the dc operating point of the circuit with inductors shorted and capacitors opened. Note: a dc analysis is automatically performed prior to a transient analysis to determine the transient initial conditions, and prior to an ac small-signal analysis to determine the linearized, small-signal models for nonlinear devices.

### 11.3. .DC Line

**General form:**

```
.DC SRCNAM VSTART VSTOP VINCR [SRC2 START2 STOP2 INCR2]
```

**Examples:**

```
.DC VIN 0.25 5.0 0.25
.DC VDS 0 10 .5 VGS 0 5 1
.DC VCE 0 10 .25 IB 0 10U 1U
```

This line defines the dc transfer curve source and sweep limits. SRCNAM is the name of an independent voltage or current source. VSTART, VSTOP, and VINCR are the starting, final, and incrementing values respectively. The first example causes the value of the voltage source VIN to be swept from 0.25 Volts to 5.0 Volts in increments of 0.25 Volts. A second source (SRC2) may optionally be specified with associated sweep parameters. In this case, the first source is swept over its range for each value of the second source. This option can be useful for obtaining semiconductor device output characteristics. See the second example circuit description in Appendix A.

### 11.4. .NODESET Line

**General form:**

```
.NODESET V(NODNUM)=VAL V(NODNUM)=VAL ...
```

**Examples:**

```
.NODESET V(12)=4.5 V(4)=2.23
```

This line helps the program find the dc or initial transient solution by making a preliminary pass with the specified nodes held to the given voltages. The restriction is then released and the iteration continues to the true solution. The .NODESET line may be necessary for convergence on bistable or astable circuits. In general, this line should not be necessary.

### 11.5. .IC Line

**General form:**

```
.IC V(NODNUM)=VAL V(NODNUM)=VAL ...
```

**Examples:**

```
.IC V(11)=5 V(4)=-5 V(2)=2.2
```

This line is for setting transient initial conditions. It has two different interpretations, depending on whether the UIC parameter is specified on the .TRAN control line. Also, one should not confuse this line with the .NODESET line. The .NODESET line is only to help dc convergence, and does not affect final bias solution (except for multi-stable circuits). The two interpretations of this line are as follows:

1. When the UIC parameter is specified on the .TRAN line, then the node voltages specified on the .IC control line are used to compute the capacitor, diode, BJT, JFET, and MOSFET initial conditions. This is equivalent to specifying the IC=... parameter on each device line, but is much more convenient. The IC=... parameter can still be specified and takes precedence over the .IC values. Since no dc bias (initial transient) solution is computed before the transient analysis, one should take care to specify all dc source voltages on the .IC control line if they are to be used to compute device initial conditions.

2. When the UIC parameter is not specified on the .TRAN control line, the dc bias (initial transient) solution is computed before the transient analysis. In this case, the node voltages specified on the .IC control line is forced to the desired initial values during the bias solution. During transient analysis, the constraint on these node voltages is removed. This is the preferred method since it allows SPICE to compute a consistent dc solution.

### 11.6. .TF Line

**General form:**

```
.TF OUTVAR INSRC
```

**Examples:**

```
.TF V(5, 3) VIN
.TF I(VLOAD) VIN
```

This line defines the small-signal output and input for the dc small- signal analysis. OUTVAR is the small-signal output variable and INSRC is the small-signal input source. If this line is included, SPICE computes the dc small-signal value of the transfer function (output/input), input resistance, and output resistance. For the first example, SPICE would compute the ratio of V(5, 3) to VIN, the small-signal input resistance at VIN, and the small-signal output resistance measured across nodes 5 and 3.

### 11.7. .AC Line

**General form:**

```
.AC DEC ND FSTART FSTOP
.AC OCT NO FSTART FSTOP
.AC LIN NP FSTART FSTOP
```

**Examples:**

```
.AC DEC 10 1 10K
.AC DEC 10 1K 100MEG
.AC LIN 100 1 100HZ
```

DEC stands for decade variation, and ND is the number of points per decade. OCT stands for octave variation, and NO is the number of points per octave. LIN stands for linear variation, and NP is the number of points. FSTART is the starting frequency, and FSTOP is the final frequency. If this line is included in the deck, SPICE performs an AC analysis of the circuit over the specified frequency range. Note that in order for this analysis to be meaningful, at least one independent source must have been specified with an ac value.

### 11.8. .DISTO Line

**General form:**

```
.DISTO DEC ND FSTART FSTOP <F2OVERF1>
.DISTO OCT NO FSTART FSTOP <F2OVERF1>
.DISTO LIN NP FSTART FSTOP <F2OVERF1>
```

**Examples:**

```
.DISTO DEC 10 1kHz 100Mhz
.DISTO DEC 10 1kHz 100Mhz 0.9
```

This line does a small-signal distortion analysis of the circuit. A multi-dimensional Volterra series analysis is done using multi-dimensional Taylor series to represent the nonlinearites at the operating point. Terms of upto third order are used in the series expansions.

If the optional parameter F2OVERF1 is not specified, .DISTO does a harmonic analysis - i.e., it analyses distortion in the circuit using only a single input frequency F1, which is swept as specified by arguments of the .DISTO command exactly as in the .AC command. Inputs at this frequency may be present at more than one input source, and their magnitudes and phases are specified by the arguments of the DISTOF1 keyword in the input file lines for the input sources (see the description for independent sources). (The arguments of the DISTOF2 keyword are not relevant in this case). The analysis produces information about the A.C. values of all node voltages and branch currents at the harmonic frequencies 2F1 and 3F1, vs. the input frequency F1 as it is swept. (A value of 1 (as a complex distortion output) signifies $\cos(2\pi(2F1)t)$ at 2F1 and $\cos(2\pi(3F1)t)$ at 3F1, using the convention that 1 at the input fundamental frequency is equivalent to $\cos(2\pi F1t)$.) The distortion component desired (2F1 or 3F1) can be selected using commands in nutmeg, and then printed or plotted. (Normally, one is interested primarily in the magnitude of the harmonic components, so the magnitude of the AC distortion value is looked at). It should be noted that these are the A.C. values of the actual harmonic components, and are not equal to HD2 and HD3. To obtain HD2 and HD3, one must divide by the corresponding A.C. values at F1, obtained from an .AC line. This division can be done using nutmeg commands.

If the optional F2OVERF1 parameter is specified, it should be a real number between (and not equal to) 0.0 and 1.0; in this case, .DISTO does a spectral analysis. It considers the circuit with sinusoidal inputs at two different frequencies F1 and F2. F1 is swept according to the .DISTO control line options exactly as in the .AC control line. F2 is kept fixed at a single frequency as F1 sweeps - the value at which it is kept fixed is equal to F2OVERF1 times FSTART. Each independent source in the circuit may potentially have two (superimposed) sinusoidal inputs for distortion, at the frequencies F1 and F2. The magnitude and phase of the F1 component are specified by the arguments of the DISTOF1 keyword in the source's input line (see the description of independent sources); the magnitude and phase of the F2 component are specified by the arguments of the DISTOF2 keyword. The analysis produces plots of all node voltages/branch currents at the intermodulation product frequencies F1 + F2, F1 - F2, and (2 F1) - F2, vs the swept frequency F1. The IM product of interest may be selected using the setplot command, and displayed with the print and plot commands. It is to be noted as in the harmonic analysis case, the results are the actual AC voltages and currents at the intermodulation frequencies, and need to be normalized with

respect to .AC values to obtain the IM parameters.

If the DISTOF1 or DISTOF2 keywords are missing from the description of an independent source, then that source is assumed to have no input at the corresponding frequency. The default values of the magnitude and phase are 1.0 and 0.0 respectively. The phase should be specified in degrees.

It should be carefully noted that the number F2OVERF1 should ideally be an irrational number, and that since this is not possible in practice, efforts should be made to keep the denominator in its fractional representation as large as possible, certainly above 3, for accurate results (i.e., if F2OVERF1 is represented as a fraction A/B, where A and B are integers with no common factors, B should be as large as possible; note that A < B because F2OVERF1 is constrained to be < 1). To illustrate why, consider the cases where F2OVERF1 is 49/100 and 1/2. In a spectral analysis, the outputs produced are at F1 + F2, F1 - F2 and 2 F1 - F2. In the latter case, F1 - F2 = F2, so the result at the F1-F2 component is erroneous because there is the strong fundamental F2 component at the same frequency. Also, F1 + F2 = 2 F1 - F2 in the latter case, and each result is erroneous individually. This problem is not there in the case where F2OVERF1 = 49/100, because F1-F2 = 51/100 F1 < > 49/100 F1 = F2. In this case, there are two very closely spaced frequency components at F2 and F1 - F2. One of the advantages of the Volterra series technique is that it computes distortions at mix frequencies expressed symbolically (i.e. n F1 ± m F2), therefore one is able to obtain the strengths of distortion components accurately even if the separation between them is very small, as opposed to transient analysis for example. The disadvantage is of course that if two of the mix frequencies coincide, the results are not merged together and presented (though this could presumably be done as a postprocessing step). Currently, the interested user should keep track of the mix frequencies himself or herself and add the distortions at coinciding mix frequencies together should it be necessary.

### 11.9. .NOISE Line

**General form:**

```
.NOISE V(OUTPUT <,REF>) SRC ( DEC |  LIN |  OCT ) PTS FSTART FSTOP
+ <PTS_PER_SUMMARY>
```

**Examples:**

```
.NOISE V(5) VIN DEC 10 1kHZ 100Mhz
.NOISE V(5,3) V1 OCT 8 1.0 1.0e6 1
```

This line does a noise analysis of the circuit. OUTPUT is the node at which the total output noise is desired; if REF is specified, then the noise voltage V(OUTPUT) - V(REF) is calculated. By default, REF is assumed to be ground. SRC is the name of an independent source to which input noise is referred. PTS, FSTART and FSTOP are .AC type parameters that specify the frequency range over which plots are desired. PTS_PER_SUMMARY is an optional integer; if specified, the noise contributions of each noise generator is produced every PTS_PER_SUMMARY frequency points.

The .NOISE control line produces two plots - one for the Noise Spectral Density curves and one for the total Integrated Noise over the specified frequency range. All noise voltages/currents are in squared

units ($V^2$/Hz and $A^2$/Hz for spectral density, $V^2$ and $A^2$ for integrated noise).

### 11.10. .TRAN Line

**General form:**

```
.TRAN TSTEP TSTOP <TSTART <TMAX>>
```

**Examples:**

```
.TRAN 1NS 100NS
.TRAN 1NS 1000NS 500NS
.TRAN 10NS 1US
```

TSTEP is the printing or plotting increment for line-printer output. For use with the post-processor, TSTEP is the suggested computing increment. TSTOP is the final time, and TSTART is the initial time. If TSTART is omitted, it is assumed to be zero. The transient analysis always begins at time zero. In the interval <zero, TSTART>, the circuit is analyzed (to reach a steady state), but no outputs are stored. In the interval <TSTART, TSTOP>, the circuit is analyzed and outputs are stored. TMAX is the maximum step-size that SPICE uses; for default, the program chooses either TSTEP or (TSTOP-TSTART)/50.0, whichever is smaller. TMAX is useful when one wishes to guarantee a computing interval which is smaller than the printer increment, TSTEP.

UIC (use initial conditions) is an optional keyword which indicates that the user does not want SPICE to solve for the quiescent operating point before beginning the transient analysis. If this keyword is specified, SPICE uses the values specified using IC=... on the various elements as the initial transient condition and proceeds with the analysis. If the .IC control line has been specified, then the node voltages on the .IC line are used to compute the initial conditions for the devices. Look at the description on the .IC control line for its interpretation when UIC is not specified.

### 11.11. .PZ Line

**General form:**

```
.PZ NODE1 NODE2 NODE3 NODE4 CUR POL
.PZ NODE1 NODE2 NODE3 NODE4 CUR ZER
.PZ NODE1 NODE2 NODE3 NODE4 CUR PZ
.PZ NODE1 NODE2 NODE3 NODE4 VOL POL
.PZ NODE1 NODE2 NODE3 NODE4 VOL ZER
.PZ NODE1 NODE2 NODE3 NODE4 VOL PZ
```

**Examples:**

```
.PZ 1 0 3 0 CUR POL
.PZ 2 3 5 0 VOL ZER
.PZ 4 1 4 1 CUR PZ
```

CUR stands for a transfer function of the type (output voltage)/(input current) while VOL stands for a transfer function of the type (output voltage)/(input voltage). POL stands for pole analysis only, ZER for zero analysis only and PZ for both. This feature is provided mainly because if there is a nonconvergence in finding poles or zeros, then, at least the other can be found. Finally, NODE1 and NODE2 are the two input nodes and NODE3 and NODE4 are the two output nodes. Thus, there is complete freedom regarding the output and input ports and the type of transfer function.

In interactive mode, the command syntax is the same except that the first field is PZ instead of .PZ. To print the results, one should use the command 'print all'.

### 11.12. .FOUR Line

**General form:**

```
.FOUR FREQ OV1 <OV2 OV3 ...>
```

**Examples:**

```
.FOUR 100K  V(5)
```

This line controls whether SPICE performs a Fourier analysis as a part of the transient analysis. FREQ is the fundamental frequency, and OV1, ..., are the output variables for which the analysis is desired. The Fourier analysis is performed over the interval <TSTOP-period, TSTOP>, where TSTOP is the final time specified for the transient analysis, and period is one period of the fundamental frequency. The dc component and the first nine harmonics are determined. For maximum accuracy, TMAX (see the .TRAN line) should be set to period/100.0 (or less for very high-Q circuits).

## 12. THE INTERACTIVE COMMAND INTERPRETOR

**Nutmeg** is a post processor for SPICE – it takes the raw output file created by **spice -r** (or with the **write** command) and plots the data on a graphics terminal or a workstation display. Most of the commands available in the interactive Spice3 front end are available in **nutmeg**; where this is not the case, Spice-only commands have been marked with an asterisk ("*"). Note that the raw output file is different from the data that Spice2 writes to the standard output.

**Spice** and **Nutmeg** use the **X Window System** for plotting if they find the environment variable **DISPLAY**. Otherwise, **MFB** (a graphics-terminal independent interface) is used. If you are using **X** on a workstation, the **DISPLAY** variable should already be set; if you want to display graphics on a system different from the one you are running **Spice3** or **Nutmeg** on, **DISPLAY** should be of the form "*machine*:0". See the appropriate documentation on the X Window Sytem for more details.

### Command Synopsis

```
spice [ -n ] [ -t term ] [ -r rawfile] [ -b ] [ -i ] [ input file ... ]

nutmeg [ - ] [ -n ] [ -t term ] [ datafile ... ]
```

Options are:

**-** Don't try to load the default data file ("rawspice.raw") if no other files are given. **Nutmeg** only.

**-n** (or **-N**)
Don't try to source the file ".spiceinit" upon startup. Normally **spice** and **nutmeg** try to find the file in the current directory, and if it is not found then in the user's home directory.

**-t term** (or **-T term**)
The program is being run on a terminal with *mfb* name **term**.

**-b** (or **-B**)
Run in batch mode. Spice3 reads the default input source (e.g. keyboard) or reads the given input file and performs the analyses specified; output is either Spice2-like line-printer plots ("ascii plots") or a spice rawfile. See the following section for details. Note that if the input source is not a terminal (e.g. using the IO redirection notation of "<") Spice3 defaults to batch mode (**-i** overrides). This option is valid for **Spice3** only.

**-s** (or **-S**)
Run in server mode. This is like batch mode, except that a temporary rawfile is used and then written to the standard output, preceded by a line with a single "@", after the simulation is done. This mode is used by the spice daemon. This option is valid for **Spice3** only.

**-i** (or **-I**)
Run in interactive mode. This is useful if the standard input is not a terminal but interactive mode is desired. Command completion is not available unless the standard input is a terminal, however. This option is valid for **Spice3** only.

**-r** *rawfile* (or **-P** *rawfile*)

Use *rawfile* as the default file into which the results of the simulation are saved. This option is valid for **Spice3** only.

Further arguments to **spice** are taken to be Spice3 input decks, which are read and saved (if running in batch mode then they are run immediately). Spice3 accepts any Spice2 input decks, and output ascii plots, fourier analyses, and node printouts as specified in .plot, .four, and .print cards. If an **out** parameter is given on a .width card, the effect is the same as **set width = ...**. Since Spice3 ascii plots do not use multiple ranges, however, if vectors together on a .plot card have different ranges they are not provide as much information as they would in Spice2. The output of Spice3 is also much less verbose than Spice2, in that the only data printed is that requested by the above cards.

For **nutmeg**, further arguments are taken to be data files in binary or ascii format (see **sconvert**(1)) which are loaded into nutmeg. If the file is in binary format, it may be only partially completed (useful for examining Spice2 ouput before the simulation is finished). One file may contain any number of data sets from different analyses.

### 12.1. Expressions, Functions, and Predefined Constants

**Spice** and **Nutmeg** data is in the form of vectors: time, voltage, etc. Each vector has a type, and vectors can be operated on and combined algebraicly in ways consistent with their types. Vectors are normally created when a data file is read in (see the **load** command below), and when the initial datafile is loaded. They can also be created with the **let** command.

An expression is an algebraic formula involving vectors and scalars (a scalar is a vector of length 1) and the following operations:

\+ - * / ^ %

% is the modulo operator, and the comma operator has two meanings: if it is present in the argument list of a user-definable function, it serves to separate the arguments. Otherwise, the term **x , y** is synonymous with **x + j(y)**.

Also available are the logical operations & (and), | (or), ! (not), and the relational operations <, >, >=, <=, =, and <> (not equal). If used in an algebraic expression they work like they would in C, producing values of 0 or 1. The relational operators have the following synonyms:

| | |
|---|---|
| **gt** | > |
| **lt** | < |
| **ge** | >= |
| **le** | <= |
| **ne** | <> |
| **eq** | = |
| **and** | & |
| **or** | \| |
| **not** | ! |

These are useful when < and > might be confused with IO redirection (which is almost always).

The following functions are available:

| | |
|---|---|
| **mag(vector)** | The magnitude of vector |
| **ph(vector)** | The phase of vector |
| **j(vector)** | *i* (sqrt(-1)) times vector |
| **real(vector)** | The real component of vector |
| **imag(vector)** | The imaginary part of vector |
| **db(vector)** | 20 log10(mag(vector)) |
| **log(vector)** | The logarithm (base 10) of vector |
| **ln(vector)** | The natural logarithm (base e) of vector |
| **exp(vector)** | e to the vector power |
| **abs(vector)** | The absolute value of vector. |
| **sqrt(vector)** | The square root of vector. |
| **sin(vector)** | The sin of vector. |
| **cos(vector)** | The cosine of vector. |
| **tan(vector)** | The tangent of vector. |
| **atan(vector)** | The inverse tangent of vector. |
| **norm(vector)** | The **vector** normalized to 1 (i.e, the largest magnitude of any component is 1). |
| **rnd(vector)** | A vector with each component a random integer between 0 and the absolute value of the vectors's corresponding component. |
| **mean(vector)** | The result is a scalar (a length 1 vector) that is the mean of the elements of **vector**. |

| | |
|---|---|
| **vector(number)** | The result is a vector of length **number**, with elements 0, 1, ... **number - 1**. If **number** is a vector then just the first element is taken, and if it isn't an integer then the floor of the magnitude is used. |
| **length(vector)** | The length of **vector**. |
| **interpolate(plot.vector)** | The result of interpolating the named vector onto the scale of the current plot. This function uses the variable **polydegree** to determine the degree of interpolation. |

A vector may be either the name of a vector already defined, a floating- point number (a scalar), or a list like **[elt1 elt2 ... eltn]**, which is a vector of length n. A number may be written in any format acceptable to SPICE, such as **14.6Meg** or **-1.231e-4**. Note that you can either use scientific notation or one of the abbreviations like *MEG* or *G*, but not both. As with SPICE, a number may have trailing alphabetic characters after it.

The notation **expr [lower upper]**, where **lower** and **upper** are numbers, denotes the range of elements from **expr** between **lower** and **upper**. The notation **expr [num]** denotes the **num**'th element of **expr**. If **upper** is lower than **lower**, the order of the elements in the vector is reversed. In all other cases, **[** and **]** serve to surround literal vectors as described above. (You may have to use a lot of parentheses to make sure that you get what you want. For instance, you have to type **print (foo) ([1 2])** to print the two vectors. Otherwise it is interpreted as a function call or a vector with an index.) Note that the expression **time[10 20][5]** does *not* yield the 15th element of **time** but rather the 5th. In general only the last index suffix on an expression has effect.

To reference vectors in a plot that is not the *current plot* (see the **setplot** command, below), the notation **plotname.vecname** can be used.

Either a plotname or a vector name may be the wildcard **all**. If the plotname is **all**, matching vectors from all plots are specified, and if the vector name is **all**, all vectors in the specified plots are referenced. Note that you may not use binary operations on expressions involving wildcards – it is not obvious what **all + all** should denote, for instance. Thus some (contrived) examples of expressions are:

```
cos(TIME) + db(v(3))
sin(cos(log([1 2 3 4 5 6 7 8 9 10])))
TIME * rnd(v(9)) - 15 * cos(vin#branch) ^ [7.9e5 8]
not ((ac3.FREQ[32] & tran1.TIME[10]) gt 3)
```

Vector names in **spice** may have a name such as **@name[param]**, where **name** is either the name of a device instance or model. This denotes the value of the **param** parameter of the device or model. See Appendix B for details of what parameters are available. The value is a vector of length 1. This function is also available with the **show** command, and is available with variables for convenience for command scripts.

There are a number of pre-defined constants in **nutmeg**. They are:

| | |
|---|---|
| **pi** | π (3.14159...) |
| **e** | The base of natural logarithms (2.71828...) |
| **c** | The speed of light (299,792,500 m/sec) |
| **i** | The square root of -1 |
| **kelvin** | Absolute 0 in Centigrade (-273.15 °C) |
| **echarge** | The charge on an electron (1.6021918e-19 C) |
| **boltz** | Boltzman's constant (1.3806226e-23) |
| **planck** | Planck's constant (h = 6.626200e-34) |

These are all in MKS units. If you have another variable with a name that conflicts with one of these then it takes precedence.

## 12.2. Command Interpretation

If a word is typed as a command, and there is no built-in command with that name, the directories in the *sourcepath* list are searched in order for the file. If it is found, it is read in as a command file (as if it were **source**d). Before it is read, however, the variables *argc* and *argv* are set to the number of words following the filename on the command line, and a list of those words respectively. After the file is finished, these variables are **unset**. Note that if a command file calls another, it must save its *argv* and *argc* since they are altered. Also, command files may not be re-entrant since there are no local variables. (Of course, the procedures may explicitly manipulate a stack...) This way one can write scripts analogous to shell scripts for **nutmeg** and Spice3.

Note that for the script to work with Spice3, it must begin with a blank line (or whatever else, since it is thrown away) and then a line with **.control** on it. This is an unfortunate result of the **source** command being used for both circuit input and command file execution. Note also that this allows the user to merely type the name of a circuit file as a command and it is automatically run.

There are various command scripts installed in */usr/local/lib/spice/scripts* (or whatever the path is on your machine), and the default *sourcepath* includes this directory, so you can use these command files (almost) like builtin commands.

## 12.3. Commands

### 12.3.1. Ac: Perform an AC, small-signal frequency response analysis *

**General Form**

`ac ( DEC | OCT | LIN )` *N Fstart Fstop*

Do an ac analysis. See the previous sections of this manual for more details.

### 12.3.2. Alias: Create an alias for a command

**General Form**

```
alias [word] [text ...]
```

Causes **word** to be aliased to **text**. History substitutions may be used, as in C-shell aliases.

### 12.3.3. Alter: Change a device parameter *

**General Form**

```
alter @device[name] = value
alter device = value
```

Alter a device parameter.

### 12.3.4. Asciiplot: Plot values using old-style character plots

**General Form**

```
asciiplot plotargs
```

Produce a line printer plot of the vectors. The plot is sent to the standard output, so you can put it into a file with *asciiplot args ... > file*. The **set** options **width, height,** and **nobreak** determine the width and height of the plot, and whether there are page breaks, respectively. Note that you will have problems if you try to **asciiplot** something with an X-scale that isn't monotonic (i.e, something like *sin(TIME)* ), because **asciiplot** uses a simple-minded linear interpolation.

### 12.3.5. Aspice: Asynchronous spice run

**General Form**

```
aspice [output-file]
```

Start a SPICE-3 run, and when it is finished load the data. The raw data is kept in a temporary file. If *output-file* is specified then the diagnostic output is directed into that file, otherwise it is thrown away.

### 12.3.6. Bug: Mail a bug report

**General Form**

```
bug
```

Send a bug report. Please include a short summary of the problem, the version number and name of the operating system that you are running, the version of Spice that you are running, and the relevant spice input file. (If you have defined BUGADDR, the mail is delivered to there.)

### 12.3.7. Cd: Change directory

**General Form**

```
cd [directory]
```

Change the current working directory to **directory**, or to the user's home directory if none is given.

### 12.3.8. Dc: Perform a DC-sweep analysis *

**General Form**

`dc` *Source-Name Vstart Vstop Vincr [ Source2 Vstart2 Vstop2 Vincr2 ]*

Do a dc transfer curve analysis. See the previous sections of this manual for more details.

### 12.3.9. Define: Define a function

**General Form**

```
define function(arg1, arg2, ...) expression
```

Define the *user-definable function* with the name *function* and arguments *arg1, arg2, ...* to be *expression*, which may involve the arguments. When the function is later used, the arguments it is given are substituted for the formal arguments when it is parsed. If *expression* is not present, any definition for *function* is printed, and if there are no arguments to *define* then all currently active definitions are printed. Note that you may have different functions defined with the same name but different arities.

Some useful definitions are:

```
define max(x,y) (x > y) * x + (x <= y) * y
define min(x,y) (x < y) * x + (x >= y) * y
```

### 12.3.10. Delete: Remove a trace or breakpoint *

**General Form**

```
delete [ debug-number ... ]
```

Delete the specified breakpoints and traces. The **debug numbers** are those shown by the **status** command (unless you do **status > file**, in which case the debug numbers are not printed).

### 12.3.11. Diff: Compare vectors

**General Form**

```
diff plot1 plot2 [vec ...]
```

Compare all the vectors in the specified *plots*, or only the named vectors if any are given. There are different vectors in the two plots, or any values in the vectors differ significantly the difference is reported. The variables **abstol, reltol,** and **vntol** are used to determine a significant difference.

### 12.3.12. Display: List known vectors and types

**General Form**

```
display [varname ...]
```

Prints a summary of currently defined vectors, or of the names specified. The vectors are sorted by name unless the variable **nosort** is set. The information given is the name of the vector, the length, the type of the vector, and whether it is real or complex data. Additionally, one vector is labeled **[scale]**. When a command such as *plot* is given without a *vs* argument, this scale is used for the X-axis. It is always the first vector in a rawfile, or the first vector defined in a new plot. If you undefine the scale (i.e, *let TIME = []*), one of the remaining vectors becomes the new scale (which is undetermined).

### 12.3.13. Echo: Print text

**General Form**

```
echo [text...]
```

Echos the given text to the screen.

### 12.3.14. Edit: Edit the current circuit *

**General Form**

```
edit [ file ]
```

Print the current Spice3 deck into a file, call up the editor on that file and allow the user to modify it, and then read it back in, replacing the original deck. If a *filename* is given, then edit that file and load it, making the circuit the current one.

### 12.3.15. Fourier: Perform a fourier transform

**General Form**

```
fourier fundamental_frequency [value ...]
```

Does a fourier analysis of each of the given values, using the first 10 multiples of the fundamental frequency (or the first *nfreqs*, if that variable is set – see below). The output is like that of the **.four** Spice3 line. The values may be any valid expression. The values are interpolated onto a fixed-space grid with the number of points given by the **fourgridsize** variable, or 200 if it is not set. The interpolation is of degree **polydegree** if that variable is set, or 1. If **polydegree** is 0, then no interpolation is done. This is likely to give erroneous results if the time scale is not monotonic, though.

### 12.3.16. Hardcopy: Save a plot to a file for printing

**General Form**

```
hardcopy file plotargs
```

Just like **plot**, except creates a file called **file** containing the plot. The file is an image in *plot(5)* format, and can be printed by either the **plot(1)** program or **lpr** with the **-g** flag.

### 12.3.17. Help: Print summaries of Spice3 commands

**General Form**

```
help [all] [command ...]
```

Prints help. If the argument **all** is given, a short description of everything you could possibly type is printed. If **command**s are given, descriptions of those commands are printed. Otherwise help for only a few major commands is printed.

### 12.3.18. History: Review previous commands

**General Form**

```
history [number]
```

Print out the history, or the last **number** commands typed at the keyboard. *Note:* in Spice3 version 3a7 and earlier, all commands (including ones read from files) were saved.

### 12.3.19. Iplot: Incremental plot *

**General Form**

```
iplot [ node ...]
```

Incrementally plot the values of the nodes while Spice3 runs. The **iplot** command can be used with the **where** command to find trouble spots in a transient simulation.

### 12.3.20. Jobs: List active asynchronous spice runs

**General Form**

```
jobs
```

Report on the asynchronous SPICE-3 jobs currently running. **Nutmeg** checks to see if the jobs are finished every time you execute a command. If it is done then the data is loaded and becomes available.

### 12.3.21. Let: Assign a value to a vector

**General Form**

```
let name = expr
```

Creates a new vector called **name** with the value specified by **expr,** an expression as described above. If **expr** is [] (a zero-length vector) then the vector becomes undefined. If there are no arguments, **let** is the same as **display**.

### 12.3.22. Linearize: Interpolate to a linear scale *

**General Form**

```
linearize vec ...
```

Create a new plot with all of the vectors in the current plot, or only those mentioned if arguments are given. The new vectors are interpolated onto a linear time scale, which is determined by the values of **tstep, tstart,** and **tstop** in the currently active transient analysis. The currently loaded deck must include a transient analysis (a **tran** command may be run interactively before the last **reset**, alternately), and the current plot must be from this transient analysis. This command is needed because Spice3 doesn't output the results from a transient analysis in the same manner that Spice2 did.

### 12.3.23. Listing: Print a listing of the current circuit *

**General Form**

```
listing [logical] [physical] [deck] [expand]
```

If the **logical** argument is given, the listing is with all continuation lines collapsed into one line, and if the **physical** argument is given the lines are printed out as they were found in the file. The default is **logical**. A **deck** listing is just like the **physical** listing, except without the line numbers it recreates the input file verbatim (except that it does not preserve case). If the word **expand** is present, the circuit is printed with all subcircuits expanded.

### 12.3.24. Load: Load rawfile data

**General Form**

```
load [filename] ...
```

Loads either binary or ascii format rawfile data from the files named. The default filename is **rawspice.raw**, or the argument to the **-r** flag if there was one.

### 12.3.25. Op: Perform an operating point analysis *

**General Form**

```
op
```

Do an operating point analysis. See the previous sections of this manual for more details.

### 12.3.26. Plot: Plot values on the display

**General Form**

```
plot exprs [ylimit ylo yhi] [xlimit xlo xhi] [xindices xilo xihi]
     [xcompress comp] [xdelta xdel] [ydelta ydel] [xlog] [ylog]
     [vs xname] [xlabel word] [ylabel word] [title word] [samep]
```

Plot the given **exprs** on the screen (if you are on a graphics terminal). The **xlimit** and **ylimit** arguments determine the high and low x- and y-limits of the axes, respectively. The **xindices** arguments determine what range of points are to be plotted – everything between the **xilo**'th point and the **xihi**'th point is plotted. The **xcompress** argument specifies that only one out of every **comp** points should be plotted. If an **xdelta** or a **ydelta** parameter is present, it specifies the spacing between grid lines on the X- and Y-axis. These parameter names may be abbreviated to **xl, yl, xind, xcomp, xdel,** and **ydel** respectively.

The **xname** argument is an expression to use as the scale on the x-axis. If **xlog** or **ylog** are present then the X or Y scale, respectively, is logarithmic. The **xlabel** and **ylabel** arguments cause the specified labels to be used for the X and Y axes, respectively.

If **samep** is given, the values of the other parameters (other than **xname**) from the previous **plot, hardcopy,** or **asciiplot** command is used unless re-defined on the command line.

The **title** argument is used in the place of the plot name at the bottom of the graph.

Finally, the keyword **polar** or **smith** can be given to generate a polar or smith grid. Note that the data is not transformed, so for smith plots you will have to plot $(x - 1) / (x + 1)$ to get the correct plot.

### 12.3.27. Print: Print values

**General Form**

```
print [col] [line] expr ...
```

Prints the vector described by the expression **expr.** If the **col** argument is present, print the vectors named side by side. If **line** is given, the vectors are printed horizontally. **col** is the default, unless all the vectors named have a length of one, in which case **line** is the default. The options **width, length,** and **nobreak** are effective for this command (see **asciiplot**). If the expression is **all**, all of the vectors available are printed. Thus **print col all > file** prints everything in the file in SPICE2 format. The scale vector (time, frequency) is always in the first column unless the variable **noprintscale** is true.

### 12.3.28. Quit: Leave Spice3 or Nutmeg

**General Form**

```
quit
```

Quit nutmeg or spice.

### 12.3.29. Rehash: Reset internal hash tables

**General Form**

```
rehash
```

Recalculate the internal hash tables used when looking up UNIX commands, and make all UNIX commands in the user's PATH available for command completion. This is useless unless you have **set unixcom** first (see above).

### 12.3.30. Reset: Reset an analysis *

**General Form**

```
reset
```

Throw out any intermediate data in the circuit (e.g, after a breakpoint or after one or more analyses have been done already), and re-parse the deck. The circuit can then be re-run. (**Note**: this command used to be **end** in Spice 3a5 and earlier versions -- **end** is now used for control structures.) The **run** command does this automatically, so this command should not be necessary.

### 12.3.31. Resume: Continue a simulation after a stop *

**General Form**

```
resume
```

Resume a simulation after a stop.

### 12.3.32. Rspice: Remote spice submission

**General Form**

```
rspice [input file]
```

Runs a SPICE-3 remotely taking the **input file** as a SPICE-3 input deck, or the current circuit if no argument is given. **Nutmeg** waits for the job to complete, and passes output from the remote job to the user's standard output. When the job is finished the data is loaded in as with aspice. If the variable *rhost* is set, **nutmeg** connects to this host instead of the default remote SPICE-3 server machine. Note that this command only works if your system administrator is running a SPICE-3 daemon on the remote host. If the variable *rprogram* is set, then **rspice** uses this as the pathname to the program to run.

### 12.3.33. Run: Run analysis from the input file *

**General Form**

```
run [rawfile]
```

Run the simulation as specified in the input file. If there were any of the control lines .ac, .op, able interactively.

### 12.3.34. Rusage: Resource usage

**General Form**

```
rusage [resource ...]
```

Print resource usage statistics. If any **resource**s are given, just print the usage of that resource. Currently valid **resource**s are:

| | |
|---|---|
| **elapsed** | The amount of time elapsed since the last **rusage elaped** call. |
| **faults** | Number of page faults and context switches (BSD only). |
| **space** | Data space used. |
| **time** | CPU time used so far. |
| **everything** | All of the above. |

### 12.3.35. Save: Save a set of outputs *

**General Form**

```
save [all] [output ...]
.save [all] [output ...]
```

Save a set of outputs, discarding the rest. If a node has been mentioned in a **save** command, it appears in the working plot after a run has completed, or in the rawfile if spice is run in batch mode. If a node is traced or plotted (see below) it is also saved. For backward compatibility, if there are **no** save commands given, all outputs are saved.

### 12.3.36. Set: Set the value of a variable

**General Form**

```
set [word] [word = value] ...
```

Set the value of **word** to be **value**, if it is present. You can set any word to be any value, numeric or string. If no value is given then the value is the boolean 'true'.

The value of *word* may be inserted into a command by writing *$word*. If a variable is set to a list of values that are enclosed in parentheses (which **must** be separated from their values by white space), the value of the variable is the list.

The variables used by nutmeg are listed in the following section.

### 12.3.37. Setcirc: Change the current circuit *

**General Form**

```
setcirc [circuit name]
```

The current circuit is the one that is used for the simulation commands below. When a circuit is loaded with the **source** command (see below) it becomes the current circuit.

### 12.3.38. Setplot: Switch the current set of vectors

**General Form**

```
setplot [plotname]
```

Set the **current plot** to the plot with the given name, or if no name is given, prompt the user with a menu. (Note that the plots are named as they are loaded, with names like **tran1** or **op2**. These names are shown by the **setplot** and **display** commands and are used by **diff**, below.) If the "New plot" item is selected, the current plot becomes one with no vectors defined.

Note that here the word "plot" refers to a group of vectors that are the result of one SPICE run. When more than one file is loaded in, or more than one plot is present in one file, **nutmeg** keeps them separate and only shows you the vectors in the current plot.

### 12.3.39. Settype: Set the type of a vector

**General Form**

```
settype type vector ...
```

Change the type of the named vectors to **type**. Type names can be found in the manual page for **sconvert**.

### 12.3.40. Shell: Call the command interpretor

**General Form**

```
shell [args ...]
```

Fork a shell, or execute the arguments as a command to the shell.

### 12.3.41. Shift: Alter a list variable

**General Form**

```
shift [varname] [number]
```

If *varname* is the name of a list variable, it is shifted to the left by *number* elements (i.e, the *number* leftmost elements are removed). The default *varname* is **argv**, and the default *number* is 1.

### 12.3.42. Show: Show a device parameter *

**General Form**

`show` *@device [* `[` *name* `]` *]*

Print a device instance or model parameter (or all parameters).

### 12.3.43. Source: Read a Spice3 input file *

**General Form**

`source` *file*

**For Spice3:** Read the Spice3 input file **file**. **Nutmeg** and Spice3 commands may be included in the file, and must be enclosed between the lines *.control* and *.endc*. These commands are executed immediately after the circuit is loaded, so a control line of *ac* ... works the same as the corresponding the circuit. The exception to this rule is the file *.spiceinit*. Thus, a Spice3 command script must begin with a blank line and then with a *.control* line. Also, any line beginning with the characters *# is considered a control line. This makes it possible to imbed commands in Spice3 input files that are ignored by earlier versions of Spice2

**For Nutmeg:** Reads commands from the file **filename.** Lines beginning with the character ***** are considered comments and ignored.

### 12.3.44. Status: Display breakpoint information *

**General Form**

`status`

Display all of the traces and breakpoints currently in effect.

### 12.3.45. Step: Run a fixed number of timepoints *

**General Form**

`step [number]`

Iterate **number** times, or once, and then stop.

### 12.3.46. Stop: Set a breakpoint *

**General Form**

```
stop [ after n] [ when value cond value ] ...
```

Set a breakpoint. The argument **after n** means stop after **n** iteration number **n**, and the argument **when** *value cond value* means stop when the first *value* is in the given relation with the second *value*, the possible relations being

| | | | |
|---|---|---|---|
| **eq** | or | = | equal to |
| **ne** | or | <> | not equal to |
| **gt** | or | > | greater than |
| **lt** | or | < | less than |
| **ge** | or | >= | greater than or equal to |
| **le** | or | <= | less than or equal to |

IO redirection is disabled for the **stop** command, since the relational operations conflict with it (it doesn't produce any output anyway). The *value*s above may be node names in the running circuit, or real values. If more than one condition is given, e.g. **stop after 4 when v(1) > 4 when v(2) < 2**, the conjunction of the conditions is implied.

### 12.3.47. Trace: Trace nodes *

**General Form**

```
trace [ node ...]
```

Every iteration the value of the node is printed to the standard output.

### 12.3.48. Tran: Perform a transient analysis *

**General Form**

```
tran Tstep Tstop [ Tstart [ Tmax ] ] [ UIC ]
```

Do a transient analysis. See the previous sections of this manual for more details.

### 12.3.49. Unalias: Retract an alias

**General Form**

```
unalias [word ...]
```

Removes any aliases present for the **word**s.

### 12.3.50. Undefine: Retract a definition

**General Form**

```
undefine function
```

Definitions for the named user-defined functions are deleted.

### 12.3.51. Unset: Clear a variable

**General Form**

```
unset [word] ...
```

Unset the variables **word**.

### 12.3.52. Version: Print the version of Spice

**General Form**

```
version [version id]
```

Print out the version of **nutmeg** that is running. If there are arguments, it checks to make sure that the arguments match the current version of SPICE. (This is mainly used as a **Command:** line in rawfiles.)

### 12.3.53. Where: Identify troublesome node or device

**General Form**

```
where
```

When performing a transient or operating point analysis, the name of the last node or device to cause non-convergence is saved. The **where** command prints out this information so that you can examine the circuit and either correct the problem or make a bug report. You may do this either in the middle of a run or after the simulator has given up on the analysis. For transient simulation, the **iplot** command can be used to monitor the progress of the analysis. When the analysis slows down severly or hangs, interrupt the simulator (with control-C) and issue the **where** command. Note that only one node or device is printed; there may be problems with more than one node.

#### 12.3.54. Write: Write data to a file

**General Form**

```
write [file] [exprs]
```

Writes out the expressions to **file.**

First vectors are grouped together by plots, and written out as such (i.e, if the expression list contained three vectors from one plot and two from another, then two plots are written, one with three vectors and one with two). Additionally, if the scale for a vector isn't present, it is automatically written out as well.

The default format is ascii, but this can be changed with the **set filetype** command. The default filename is **rawspice.raw**, or the argument to the **-r** flag on the command line, if there was one, and the default expression list is **all**.

### 12.4. Control Structures

#### 12.4.1. While — End

**General Form**

```
while condition
      statement
      ...
end
```

While *condition*, an arbitrary algebraic expression, is true, execute the statements.

#### 12.4.2. Repeat — End

**General Form**

```
repeat [number]
      statement
      ...
end
```

Execute the statements *number* times, or forever if no argument is given.

### 12.4.3. Dowhile — End

**General Form**

```
dowhile condition
      statement
      ...
end
```

The same as **while**, except that the *condition* is tested after the statements are executed.

### 12.4.4. Foreach — End

**General Form**

```
foreach var value ...
      statement
      ...
end
```

The statements are executed once for each of the *value*s, each time with the variable *var* set to the current one. (*var* can be accessed by the $*var* notation – see below).

### 12.4.5. If — Then — Else

**General Form**

```
if condition
      statement
      ...
else
      statement
      ...
end
```

If the *condition* is non-zero then the first set of statements are executed, otherwise the second set. The **else** and the second set of statements may be omitted.

### 12.4.6. Label

**General Form**

```
label word
```

If a statement of the form `goto` *word* is encountered, control is transferred to this point, otherwise this is a no-op.

### 12.4.7. Goto

**General Form**

`goto` *word*

If a statement of the form `label` *word* is present in the block or an enclosing block, control is transferred there. Note that if the label is at the top level, it *must* be before the `goto` statement (i.e, a forward `goto` may occur only within a block).

### 12.4.8. Continue

**General Form**

`continue`

If there is a **while, dowhile,** or **foreach** block enclosing this statement, control passes to the test, or in the case of **foreach**, the next value is taken. Otherwise an error results.

### 12.4.9. Break

**General Form**

`break`

If there is a **while, dowhile,** or **foreach** block enclosing this statement, control passes out of the block. Otherwise an error results.

Of course, control structures may be nested. When a block is entered and the input is the terminal, the prompt becomes a number of >'s corresponding to the number of blocks the user has entered. The current control structures may be examined with the debugging command **cdump.**

## 12.5. Variables

The variables meaningful to **nutmeg** which may be altered by the **set** command are:

| | |
|---|---|
| **abstol** | The absolute tolerance used by the **diff** command. |
| **appendwrite** | Append to the file when a **write** command is issued, if one already exists. |
| **color***N* | These variables determine the colors used, if **X** is being run on a color display. *N* may be between 0 and 15. Color 0 is the background, color 1 is the grid and text color, and colors 2 through 15 are used in order for vectors plotted. The value of the **color** variables should be names of colors, which may be found in the file **/usr/lib/rgb.txt**. |
| **combplot** | Plot vectors by drawing a vertical line from each point to the X-axis, as opposed to joining the points. Note that this option is subsumed in the *plottype* option, below. |
| **cpdebug** | Print *cshpar* debugging information (must be complied with the -DCPDEBUG flag). Unsupported in the current release. |
| **debug** | If set then a lot of debugging information is printed (must be compiled with the -DFTEDEBUG flag). Unsupported in the current release. |
| **device** | The name (/dev/tty??) of the graphics device. If this variable isn't set then the user's terminal is used. To do plotting on another monitor you probably have to set both the **device** and **term** variables. (If **device** is set to the name of a file, **nutmeg** dumps the graphics control codes into this file -- this is useful for saving plots.) |
| **echo** | Print out each command before it is executed. |
| **filetype** | This can be either **ascii** or **binary,** and determines what format are. The default is **ascii.** |
| **fourgridsize** | How many points to use for interpolating into when doing fourier analysis. |
| **gridsize** | If this variable is set to an integer, this number is used as the number of equally spaced points to use for the Y-axis when plotting. Otherwise the current scale is used (which may not have equally spaced points). If the current scale isn't strictly monotonic, then this option has no effect. |
| **hcopydev** | If this is set, when the **hardcopy** command is run the resulting file is automatically printed on the printer named **hcopydev** with the command *lpr -P***hcopydev** *-g* **file**. |

**hcopydevtype** This variable specifies the type of the printer output to use in the **hardcopy** command. If hcopydevtype is not set, plot (5) format is assumed. The standard distribution currently recognizes **postscript** as an alternative output format. When used in conjunction with **hcopydev**, **hcopydevtype** should specify a format supported by the printer.

**height** The length of the page for **asciiplot** and **print col**.

**history** The number of events to save in the history list.

**nfreqs** The number of frequencies to compute in the **fourier** command. (Defaults to 10.)

**nobreak** Don't have **asciiplot** and **print col** break between pages.

**noasciiplotvalue** Don't print the first vector plotted to the left when doing an **asciiplot**.

**noclobber** Don't overwrite existing files when doing IO redirection.

**noglob** Don't expand the global characters '*', '?', '[', and ']'. This is the default.

**nogrid** Don't plot a grid when graphing curves (but do label the axes).

**nomoremode** If **nomoremode** is not set, whenever a large amount of data is being printed to the screen (e.g, the **print** or **asciiplot** commands), the output is stopped every screenful and continues when a carriage return is typed. If **nomoremode** is set then data scrolls off the screen without check.

**nonomatch** If **noglob** is unset and a global expression cannot be matched, use the global characters literally instead of complaining.

**nosort** Don't have **display** sort the variable names.

**noprintscale** Don't print the scale in the leftmost column when a **print col** command is given.

**numdgt** The number of digits to print when printing tables of data (**fourier, print col**). The default precision is 6 digits. On the VAX, approximately 16 decimal digits are available using double precision, so **numdgt** should not be more than 16. If the number is negative, one fewer digit is printed to ensure constant widths in tables.

**plottype** This should be one of **normal**, **comb**, or **point:***chars*. **normal**, the default, causes points to be plotted as parts of connected lines. **comb** causes a comb plot to be done (see the description of the **combplot** variable above). **point** causes each point to be plotted separately – the **chars** are a list of characters that are used for each vector plotted. If they are omitted then a default set is used.

**polydegree** The degree of the polynomial that the **plot** command should fit to the data. If *polydegree* is N, then **nutmeg** fits a degree N polynomial to every set of N points and draw 10 intermediate points in between each endpoint. If the points aren't monotonic, then it trys rotating the curve and reducing the degree until a fit is achieved.

**polysteps** The number of points to interpolate between every pair of points available when doing curve fitting. The default is 10.

**program** The name of the current program (*argv[0]*).

**prompt** The prompt, with the character '!' replaced by the current event number.

**rawfile** The default name for rawfiles created.

**reltol** The relative tolerance used by the **diff** command.

**rhost** The machine to use for remote SPICE-3 runs, instead of the default one (see the description of the **rspice** command, below).

**rprogram** The name of the remote program to use in the **rspice** command.

**slowplot** Stop between each graph plotted and wait for the user to type return before continuing.

**sourcepath** A list of the directories to search when a **source** command is given. The default is the current directory and the standard spice library (*/usr/local/lib/spice*, or whatever **LIBPATH** is #defined to in the Spice3 source.

**spicepath** The program to use for the **aspice** command. The default is /cad/bin/spice.

**term** The *mfb* name of the current terminal.

**units** If this is **degrees**, then all the trig functions will use degrees instead of radians.

**unixcom** If a command isn't defined, try to execute it as a UNIX command. Setting this option has the effect of giving a **rehash** command, below. This is useful for people who want to use **nutmeg** as a login shell.

**verbose** Be verbose. This is midway between **echo** and **debug** / **cpdebug**.

**vntol** The absolute voltage tolerance used by the **diff** command.

**width** The width of the page for **asciiplot** and **print col**.

**xbrushheight** The height of the brush to use if **X** is being run.

**xbrushwidth** The width of the brush to use if **X** is being run.

**xfont** The name of the X font to use when plotting data and entering labels. The plot may not look good if this is a variable-width font.

There are several **set** variables that Spice3 uses but Nutmeg does not. They are:

| | |
|---|---|
| **editor** | The editor to use for the **edit** command. |
| **modelcard** | The name of the model card (normally **.model**). |
| **noaskquit** | Do not check to make sure that there are no circuits suspended and no plots unsaved. Normally Spice3 warns the user when he tries to quit if this is the case. |
| **nobjthack** | Assume that BJT's have 4 nodes. |
| **noparse** | Don't attempt to parse decks when they are read in (useful for debugging). Of course, they cannot be run if they are not parsed. |
| **nosubckt** | Don't expand subcircuits. |
| **renumber** | Renumber input lines when a deck has **.include**'s. |
| **subend** | The card to end subcircuits (normally **.ends**). |
| **subinvoke** | The prefix to invoke subcircuits (normally **x**). |
| **substart** | The card to begin subcircuits (normally **.subckt**). |

### 12.6. Miscellaneous

If there are subcircuits in the input file, Spice3 expands instances of them. A subcircuit is delimited by the cards **.subckt** and **.ends,** or whatever the value of the variables **substart** and **subend** is, respectively. An instance of a subcircuit is created by specifying a device with type 'x' – the device line is written

```
xname node1 node2 ... subcktname
```

where the nodes are the node names that replace the formal parameters on the **.subckt** line. All nodes that are not formal parameters are prepended with the name given to the instance and a ':', as are the names of the devices in the subcircuit. If there are several nested subcircuits, node and device names look like **subckt1:subckt2:...:name**. If the variable **subinvoke** is set, then it is used as the prefix that specifies instances of subcircuits, instead of 'x'.

Nutmeg occasionally checks to see if it is getting close to running out of space, and warns the user if this is the case. (This is more likely to be useful with the SPICE front end.)

C-shell type quoting with "" and '', and backquote substitution may be used. Within single quotes, no further substitution (like history substitution) is done, and within double quotes, the words are kept together but further substitution is done. Any text between backquotes is replaced by the result of executing the text as a command to the shell.

Tenex-style ('set filec' in the 4.3 C-shell) command, filename, and keyword completion is possible: If EOF (control-D) is typed after the first character on the line, a list of the commands or possible arguments is printed (If it is alone on the line it exits **nutmeg**). If escape is typed, then **nutmeg** trys to complete what the user has already typed. To get a list of all commands, the user should type <space> ^D.

The values of variables may be used in commands by writing **$varname** where the value of the variable is to appear. The special variables *$$* and *$<* refer to the process ID of the program and a line of input which is read from the terminal when the variable is evaluated, respectively. If a variable has a name of

the form **$&word**, then **word** is considered a vector (see above), and its value is taken to be the value of the variable. If *$foo* is a valid variable, and is of type **list**, then the expression *$foo[low-high]* represents a range of elements. Either the upper index or the lower may be left out, and the reverse of a list may be obtained with *$foo[len-0]*. Also, the notation *$?foo* evaluates to 1 if the variable *foo* is defined, 0 otherwise, and *$#foo* evaluates to the number of elements in *foo* if it is a list, 1 if it is a number or string, and 0 if it is a boolean variable.

History substitutions, similar to C-shell history substitutions, are also available – see the C-shell manual page for all of the details.

The characters ~, {, and } have the same effects as they do in the C-Shell, i.e., home directory and alternative expansion. It is possible to use the wildcard characters *, ?, [, and ] also, but only if you **unset noglob** first. This makes them rather useless for typing algebraic expressions, so you should **set noglob** again after you are done with wildcard expansion. Note that the pattern **[^abc]** matchs all characters *except* **a, b,** *and* **c.**

IO redirection is available – the symbols **>, >>, >&, >>&,** and < have the same effects as in the C-shell.

You may type multiple commands on one line, separated by semicolons.

If you want to use a different **mfbcap** file than the default (usually **~cad/lib/mfbcap**), you have to set the environment variable **SPICE_MFBCAP** before you start **nutmeg** or **spice**. The **-m** option and the **mfbcap** variable no longer work.

If **X** is being used, the cursor may be positioned at any point on the screen when the window is up and characters typed at the keyboard are added to the window at that point. The window may then be sent to a printer using the **xpr(1)** program.

**Nutmeg** can be run under VAX/VMS, as well as several other operating systems. Some features like command completion, expansion of *, ?, and [], backquote substitution, the shell command, and so forth do not work.

On some systems you have to respond to the -*more*- prompt during plot with a carriage return instead of any key as you can do on UNIX.

### 12.7. Bugs

The label entry facilities are very primitive – after all, **nutmeg** isn't a graphics editor (yet). You must be careful to type very slowly when entering labels -- **nutmeg** checks the **X** event queue once every second, and can get very confused if characters arrive faster than that. Sad but true.

If you redefine colors after creating a plot window with X, and then cause the window to be redrawn, it does not redraw in the correct colors.

When defining aliases like

```
alias pdb plot db( '!:1' - '!:2' )
```

you must be careful to quote the argument list substitutions in this manner. If you quote the whole argument it might not work properly.

In a user-defined function, the arguments cannot be part of a name that uses the *plot.vec* syntax. For example:

```
define check(v(1)) cos(tran1.v(1))
```

does **not** work.

If you type **plot all all**, or otherwise use a wildcard reference for one plot twice in a command, the effect is unpredictable.

The **asciiplot** command doesn't deal with log scales or the **delta** keywords.

Often the names of terminals recognized by **MFB** are different from those in /etc/termcap. Thus you may have to reset your terminal type with the command

**set term = termname**

where **termname** is the name in the **mfbcap** file.

The **hardcopy** command is useless on VMS and other systems without the **plot** command, unless the user has a program that understands *plot(5)* format.

Spice3 recognizes all the notations used in SPICE2 **.plot** cards, and translates **vp(1)** into **ph(v(1))**, and so forth. However, if there are spaces in these names it won't work. Hence **v(1, 2)** and **(-.5, .5)** aren't recognized.

BJT's can have either 3 or 4 nodes, which makes it difficult for the subcircuit expansion routines to decide what to rename. If the fourth parameter has been declared as a model name, then it is assumed that there are 3 nodes, otherwise it is considered a node. To disable this, you can set the variable "nobjthack", which forces BJT's to have 4 nodes (for the purposes of subcircuit expansion, at least).

The **@name[param]** notation might not work with **trace, iplot,** etc. yet. The first line of a command file (except for the *.spiceinit* file) should be a comment. Otherwise SPICE may create an empty circuit structure.

Spice3 files specified on the command line are read in before the **.spiceinit** file is read. Thus if you define aliases there that you call in a Spice3 source file mentioned on the command line, they won't be recognized.

## 13. BATCH SPICE

Batch mode is entered when either the **-b** option is given or when the default input source is redirected from a file. In batch mode, the analyses specified by the control lines in the input file (e.g. ".ac", ".tran", etc.) are immediately executed. If the **-r** *rawfile* option is given then a Spice **rawfile** is written; the rawfile may be read by either the interactive mode of Spice3 or by **nutmeg**; see the previous section for details.

If a rawfile is not specified, then output plots (in line-printer form) and tables can be printed according to the .PLOT and .PRINT control lines, described next.

**.PLOT and .PRINT lines are meant for backward compatibility with Spice2.**

### 13.1. .PRINT Lines

**General form:**

```
.PRINT PRTYPE OV1 <OV2 ... OV8>
```

**Examples:**

```
.PRINT TRAN V(4) I(VIN)
.PRINT DC V(2) I(VSRC) V(23, 17)
.PRINT AC VM(4, 2) VR(7) VP(8, 3)
```

This line defines the contents of a tabular listing of one to eight output variables. PRTYPE is the type of the analysis (DC, AC, TRAN, NOISE, or DISTO) for which the specified outputs are desired. The form for voltage or current output variables is the same as given in the previous section for the **print** command; Spice2 restricts the output variable to the following forms (though this restriction is not enforced by Spice3):

`V(N1<,N2>)`

specifies the voltage difference between nodes N1 and N2. If N2 (and the preceding comma) is omitted, ground (0) is assumed. See the **print** command in the previous section for more details. For compatability with spice2, the following five additional values can be accessed for the ac analysis by replacing the "V" in `V(N1,N2)` with:

| | | |
|---|---|---|
| VR | - | real part |
| VI | - | imaginary part |
| VM | - | magnitude |
| VP | - | phase |
| VDB | - | 20 log10(magnitude) |

`I(VXXXXXXX)`

specifies the current flowing in the independent voltage source named VXXXXXXX. Positive current flows from the positive node, through the source, to the negative node. For the ac

analysis, the corresponding replacements for the letter I may be made in the same way as described for voltage outputs.

Output variables for the noise and distortion analyses have a different general form from that of the other analyses.

There is no limit on the number of .PRINT lines for each type of analysis.

### 13.2. .PLOT Lines

**General form:**

```
.PLOT PLTYPE OV1 <(PLO1, PHI1)> <OV2 <(PLO2, PHI2)> ... OV8>
```

**Examples:**

```
.PLOT DC V(4) V(5) V(1)
.PLOT TRAN V(17, 5) (2, 5) I(VIN) V(17) (1, 9)
.PLOT AC VM(5) VM(31, 24) VDB(5) VP(5)
.PLOT DISTO HD2 HD3(R) SIM2
.PLOT TRAN V(5, 3) V(4) (0, 5) V(7) (0, 10)
```

This line defines the contents of one plot of from one to eight output variables. PLTYPE is the type of analysis (DC, AC, TRAN, NOISE, or DISTO) for which the specified outputs are desired. The syntax for the OVI is identical to that for the .PRINT line and for the **plot** command in the interactive mode.

The overlap of two or more traces on any plot is indicated by the letter X.

When more than one output variable appears on the same plot, the first variable specified is printed as well as plotted. If a printout of all variables is desired, then a companion .PRINT line should be included.

There is no limit on the number of .PLOT lines specified for each type of analysis.

## 14. BIBLIOGRAPHY

[1] A. Vladimirescu and S. Liu, *The Simulation of MOS Integrated Circuits Using SPICE2*
ERL Memo No. ERL M80/7, Electronics Research Laboratory
University of California, Berkeley, October 1980

[2] T. Sakurai and A. R. Newton, *A Simple MOSFET Model for Circuit Analysis and its application to CMOS gate delay analysis and series-connected MOSFET Structure*
ERL Memo No. ERL M90/19, Electronics Research Laboratory,
University of California, Berkeley, March 1990

[3] B. J. Sheu, D. L. Scharfetter, and P. K. Ko, *SPICE2 Implementation of BSIM*
ERL Memo No. ERL M85/42, Electronics Research Laboratory
University of California, Berkeley, May 1985

[4] J. R. Pierret, *A MOS Parameter Extraction Program for the BSIM Model*
ERL Memo Nos. ERL M84/99 and M84/100, Electronics Research Laboratory
University of California, Berkeley, November 1984

[5] Min-Chie Jeng, *Design and Modeling of Deep-Submicrometer MOSFETSs*
ERL Memo Nos. ERL M90/90, Electronics Research Laboratory
University of California, Berkeley, October 1990

[6] H.Statz et al., *GaAs FET Device and Circuit Simulation in SPICE*,
IEEE Transactions on Electron Devices, V34, Number 2, February, 1987 pp160-169.

[7] Soyeon Park, *Analysis and SPICE implementation of High Temperature Effects on MOSFET*,
Master's thesis, University of California, Berkeley, December 1986.

[8] Clement Szeto, *Simulator of Temperature Effects in MOSFETs (STEIM)*,
Master's thesis, University of California, Berkeley, May 1988.

[9] J.S. Roychowdhury and D.O. Pederson, *Efficient Transient Simulation of Lossy Interconnect*,
to appear in Proceedings of the 28th ACM/IEEE Design Automation Conference, June 17-21 1991, San Francisco

# A. APPENDIX A: EXAMPLE CIRCUITS

## A.1. Circuit 1: Differential Pair

The following deck determines the dc operating point of a simple differential pair. In addition, the ac small-signal response is computed over the frequency range 1Hz to 100MEGHz.

```
SIMPLE DIFFERENTIAL PAIR
VCC  7  0    12
VEE  8  0    -12
VIN  1  0    AC 1
RS1  1  2    1K
RS2  6  0    1K
Q1   3  2  4 MOD1
Q2   5  6  4 MOD1
RC1  7  3    10K
RC2  7  5    10K
RE   4  8    10K
.MODEL MOD1 NPN BF=50 VAF=50 IS=1.E-12 RB=100 CJC=.5PF TF=.6NS
.TF V(5) VIN
.AC DEC 10 1 100MEG
.END
```

## A.2. Circuit 2: MOSFET Characterization

The following deck computes the output characteristics of a MOSFET device over the range 0-10V for VDS and 0-5V for VGS.

```
MOS OUTPUT CHARACTERISTICS
.OPTIONS NODE NOPAGE
VDS  3  0
VGS  2  0
M1   1  2  0  0 MOD1 L=4U W=6U AD=10P AS=10P
* VIDS MEASURES ID, WE COULD HAVE USED VDS, BUT ID WOULD BE NEGATIVE
VIDS 3  1
.MODEL MOD1 NMOS VTO=-2 NSUB=1.0E15 UO=550
.DC VDS 0 10 .5 VGS 0 5 1
.END
```

### A.3. Circuit 3: RTL Inverter

The following deck determines the dc transfer curve and the transient pulse response of a simple RTL inverter. The input is a pulse from 0 to 5 Volts with delay, rise, and fall times of 2ns and a pulse width of 30ns. The transient interval is 0 to 100ns, with printing to be done every nanosecond.

```
SIMPLE RTL INVERTER
VCC  4  0    5
VIN  1  0    PULSE 0 5 2NS 2NS 2NS 30NS
RB   1  2    10K
Q1   3  2  0 Q1
RC   3  4    1K
.MODEL Q1 NPN BF 20 RB 100 TF .1NS CJC 2PF
.DC VIN 0 5 0.1
.TRAN 1NS 100NS
.END
```

### A.4. Circuit 4: Four-Bit Binary Adder

The following deck simulates a four-bit binary adder, using several subcircuits to describe various pieces of the overall circuit.

```
ADDER - 4 BIT ALL-NAND-GATE BINARY ADDER

*** SUBCIRCUIT DEFINITIONS
.SUBCKT NAND 1 2 3 4
*   NODES:  INPUT(2), OUTPUT, VCC
Q1        9  5  1 QMOD
D1CLAMP   0  1    DMOD
Q2        9  5  2 QMOD
D2CLAMP   0  2    DMOD
RB        4  5    4K
R1        4  6    1.6K
Q3        6  9  8 QMOD
R2        8  0    1K
RC        4  7    130
Q4        7  6 10 QMOD
DVBEDROP 10  3    DMOD
Q5        3  8  0 QMOD
.ENDS NAND

.SUBCKT ONEBIT 1 2 3 4 5 6
*   NODES:  INPUT(2), CARRY-IN, OUTPUT, CARRY-OUT, VCC
X1   1  2  7  6   NAND
X2   1  7  8  6   NAND
X3   2  7  9  6   NAND
X4   8  9 10  6   NAND
```

```
X5   3 10 11  6   NAND
X6   3 11 12  6   NAND
X7  10 11 13  6   NAND
X8  12 13  4  6   NAND
X9  11  7  5  6   NAND
.ENDS ONEBIT

.SUBCKT TWOBIT 1 2 3 4 5 6 7 8 9
*   NODES:  INPUT - BIT0(2) / BIT1(2), OUTPUT - BIT0 / BIT1,
*           CARRY-IN, CARRY-OUT, VCC
X1   1  2  7  5 10  9   ONEBIT
X2   3  4 10  6  8  9   ONEBIT
.ENDS TWOBIT

.SUBCKT FOURBIT 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15
*   NODES:  INPUT - BIT0(2) / BIT1(2) / BIT2(2) / BIT3(2),
*           OUTPUT - BIT0 / BIT1 / BIT2 / BIT3, CARRY-IN, CARRY-OUT, VCC
X1   1  2  3  4  9 10 13 16 15   TWOBIT
X2   5  6  7  8 11 12 16 14 15   TWOBIT
.ENDS FOURBIT

*** DEFINE NOMINAL CIRCUIT
.MODEL DMOD D
.MODEL QMOD NPN(BF=75 RB=100 CJE=1PF CJC=3PF)
VCC   99  0   DC 5V
VIN1A  1  0   PULSE(0 3 0 10NS 10NS   10NS   50NS)
VIN1B  2  0   PULSE(0 3 0 10NS 10NS   20NS  100NS)
VIN2A  3  0   PULSE(0 3 0 10NS 10NS   40NS  200NS)
VIN2B  4  0   PULSE(0 3 0 10NS 10NS   80NS  400NS)
VIN3A  5  0   PULSE(0 3 0 10NS 10NS  160NS  800NS)
VIN3B  6  0   PULSE(0 3 0 10NS 10NS  320NS 1600NS)
VIN4A  7  0   PULSE(0 3 0 10NS 10NS  640NS 3200NS)
VIN4B  8  0   PULSE(0 3 0 10NS 10NS 1280NS 6400NS)
X1     1  2  3  4  5  6  7  8  9 10 11 12  0 13 99 FOURBIT
RBIT0  9  0   1K
RBIT1 10  0   1K
RBIT2 11  0   1K
RBIT3 12  0   1K
RCOUT 13  0   1K

*** (FOR THOSE WITH MONEY (AND MEMORY) TO BURN)
.TRAN 1NS 6400NS
.END
```

### A.5. Circuit 5: Transmission-Line Inverter

The following deck simulates a transmission-line inverter. Two transmission-line elements are required since two propagation modes are excited. In the case of a coaxial line, the first line (T1) models the inner conductor with respect to the shield, and the second line (T2) models the shield with respect to the outside world.

```
TRANSMISSION-LINE INVERTER
V1   1  0         PULSE(0 1 0 0.1N)
R1   1  2         50
X1   2  0  0  4   TLINE
R2   4  0         50

.SUBCKT TLINE 1 2 3 4
T1   1  2  3  4   Z0=50 TD=1.5NS
T2   2  0  4  0   Z0=100 TD=1NS
.ENDS TLINE

.TRAN 0.1NS 20NS
.END
```

## B. APPENDIX B: MODEL AND DEVICE PARAMETERS

The following tables summarize the parameters available on each of the devices and models in . There are up to four tables for each type of device supported by . Input parameters to instances and models are simply parameter that can occur on an instance or model definition line in the form ‘‘keyword=value’’ where ‘‘keyword’’ is the parameter name as given in the tables. Output parameters are those additional parameters which are available for many types of instances for the output of operating point and debugging information. These parameters are specified as ‘‘@device[keyword]’’ and are available for the most recent point computed or, if specified in a ‘‘.save’’ statement, for an entire simulation as a normal output vector. Thus, to monitor the gate-to-source capacitance of a MOSFET, a command

save @m1[cgs]

given before a transient simulation causes the specified capacitance value to be saved at each timepoint, and a subsequent command such as

plot @m1[cgs]

produces the desired plot.

Some variables are listed as both input and output, and their output simply returns the previously input value, or the default value **after** the simulation has been run. Some parameter are input only because the output system can not handle variables of the given type yet, or the need for them as output variables has not been apparent. Many such input variables are available as output variables in a different format, such as the initial condition vectors that can be retrieved as individual initial condition values. Finally, internally derived values are output only and are provided for debugging and operating point output purposes.

Please note that these tables do **not** provide the detailed information available about the parameters provided in the section on each device and model, but are provided as a quick reference guide.

### B.1. ASRC: Arbitrary Source

| ASRC — instance input-only parameters | |
|---|---|
| i | Current source |
| v | Voltage source |

| ASRC — instance output-only parameters | |
|---|---|
| pos_node | Positive Node |
| neg_node | Negative Node |

### B.2. BJT: Bipolar Junction Transistor

| BJT — instance input-only parameters | |
|---|---|
| ic | Initial condition vector |
| sens_area | flag to request sensitivity WRT area |

| BJT — instance input-output parameters | |
|---|---|
| off | Device initially off |
| icvbe | Initial B-E voltage |
| icvce | Initial C-E voltage |
| area | Area factor |
| temp | instance temperature |

| BJT — instance output-only parameters | |
|---|---|
| colnode | Number of collector node |
| basenode | Number of base node |
| emitnode | Number of emitter node |
| substnode | Number of substrate node |
| colprimenode | Internal collector node |
| baseprimenode | Internal base node |
| emitprimenode | Internal emitter node |
| vbe | B-E voltage |
| vbc | B-C voltage |
| cc | Current at collector node |
| cb | Current at base node |
| gpi | Small signal input conductance - pi |
| gmu | Small signal conductance - mu |
| gm | Small signal transconductance |
| go | Small signal output conductance |
| qbe | Charge storage B-E junction |

*continued*

| BJT — instance output-only parameters — *continued* | |
|---|---|
| cqbe | Cap. due to charge storage in B-E jct. |
| qbc | Charge storage B-C junction |
| cqbc | Cap. due to charge storage in B-C jct. |
| qcs | Charge storage C-S junction |
| cqcs | Cap. due to charge storage in C-S jct. |
| qbx | Charge storage B-X junction |
| cqbx | Cap. due to charge storage in B-X jct. |
| gx | Conductance from base to internal base |
| cexbc | Total Capacitance in B-X junction |
| geqcb | d(Ibe)/d(Vbc) |
| gccs | Internal C-S cap. equiv. cond. |
| geqbx | Internal C-B-base cap. equiv. cond. |
| ce | Emitter current |
| cs | Substrate current |
| p | Power dissipation |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | dc sens. & imag part of ac sens. |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

| BJT — model input-output parameters | |
|---|---|
| npn | NPN type device |
| pnp | PNP type device |
| is | Saturation Current |
| bf | Ideal forward beta |
| nf | Forward emission coefficient |
| vaf | Forward Early voltage |
| va | Forward Early voltage |
| ikf | Forward beta roll-off corner current |
| ik | Forward beta roll-off corner current |
| ise | B-E leakage saturation current |
| c2 | Obsolete parameter name |
| ne | B-E leakage emission coefficient |
| br | Ideal reverse beta |
| nr | Reverse emission coefficient |
| var | Reverse Early voltage |
| vb | Reverse Early voltage |
| ikr | reverse beta roll-off corner current |
| isc | B-C leakage saturation current |
| c4 | Obsolete parameter name |
| nc | B-C leakage emission coefficient |

*continued*

| BJT — model input-output parameters — *continued* | |
|---|---|
| rb | Zero bias base resistance |
| irb | Current for base resistance=(rb+rbm)/2 |
| rbm | Minimum base resistance |
| re | Emitter resistance |
| rc | Collector resistance |
| cje | Zero bias B-E depletion capacitance |
| vje | B-E built in potential |
| pe | B-E built in potential |
| mje | B-E junction grading coefficient |
| me | B-E junction grading coefficient |
| tf | Ideal forward transit time |
| xtf | Coefficient for bias dependence of TF |
| vtf | Voltage giving VBC dependence of TF |
| itf | High current dependence of TF |
| ptf | Excess phase |
| cjc | Zero bias B-C depletion capacitance |
| vjc | B-C built in potential |
| pc | B-C built in potential |
| mjc | B-C junction grading coefficient |
| mc | B-C junction grading coefficient |
| xcjc | Fraction of B-C cap to internal base |
| tr | Ideal reverse transit time |
| cjs | Zero bias C-S capacitance |
| ccs | Zero bias C-S capacitance |
| vjs | Substrate junction built in potential |
| ps | Substrate junction built in potential |
| mjs | Substrate junction grading coefficient |
| ms | Substrate junction grading coefficient |
| xtb | Forward and reverse beta temp. exp. |
| eg | Energy gap for IS temp. dependency |
| xti | Temp. exponent for IS |
| fc | Forward bias junction fit parameter |
| tnom | Parameter measurement temperature |
| kf | Flicker Noise Coefficient |
| af | Flicker Noise Exponent |

| BJT — model output-only parameters | |
|---|---|
| invearlyvoltf | Inverse early voltage:forward |
| invearlyvoltr | Inverse early voltage:reverse |
| invrollofff | Inverse roll off - forward |
| invrolloffr | Inverse roll off - reverse |
| collectorconduct | Collector conductance |
| emitterconduct | Emitter conductance |
| transtimevbcfact | Transit time VBC factor |
| excessphasefactor | Excess phase fact. |

### B.3. BSIM1: Berkeley Short Channel IGFET Model

| BSIM1 — instance input-only parameters | |
|---|---|
| ic | Vector of DS,GS,BS initial voltages |

| BSIM1 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Number of squares in drain |
| nrs | Number of squares in source |
| off | Device is initially off |
| vds | Initial D-S voltage |
| vgs | Initial G-S voltage |
| vbs | Initial B-S voltage |

| BSIM1 — model input-only parameters | |
|---|---|
| nmos | Flag to indicate NMOS |
| pmos | Flag to indicate PMOS |

| BSIM1 — model input-output parameters | |
|---|---|
| vfb | Flat band voltage |
| lvfb | Length dependence of vfb |
| wvfb | Width dependence of vfb |
| phi | Strong inversion surface potential |
| lphi | Length dependence of phi |
| wphi | Width dependence of phi |
| k1 | Bulk effect coefficient 1 |
| lk1 | Length dependence of k1 |
| wk1 | Width dependence of k1 |
| k2 | Bulk effect coefficient 2 |
| lk2 | Length dependence of k2 |
| wk2 | Width dependence of k2 |
| eta | VDS dependence of threshold voltage |
| leta | Length dependence of eta |
| weta | Width dependence of eta |
| x2e | VBS dependence of eta |
| lx2e | Length dependence of x2e |
| wx2e | Width dependence of x2e |
| x3e | VDS dependence of eta |
| lx3e | Length dependence of x3e |
| wx3e | Width dependence of x3e |
| dl | Channel length reduction in um |
| dw | Channel width reduction in um |
| muz | Zero field mobility at VDS=0 VGS=VTH |
| x2mz | VBS dependence of muz |
| lx2mz | Length dependence of x2mz |
| wx2mz | Width dependence of x2mz |
| mus | Mobility at VDS=VDD VGS=VTH, channel length modulation |
| lmus | Length dependence of mus |
| wmus | Width dependence of mus |
| x2ms | VBS dependence of mus |
| lx2ms | Length dependence of x2ms |
| wx2ms | Width dependence of x2ms |
| x3ms | VDS dependence of mus |
| lx3ms | Length dependence of x3ms |
| wx3ms | Width dependence of x3ms |
| u0 | VGS dependence of mobility |
| lu0 | Length dependence of u0 |
| wu0 | Width dependence of u0 |
| x2u0 | VBS dependence of u0 |
| lx2u0 | Length dependence of x2u0 |
| wx2u0 | Width dependence of x2u0 |

*continued*

| BSIM1 — model input-output parameters — *continued* | |
|---|---|
| u1 | VDS depence of mobility, velocity saturation |
| lu1 | Length dependence of u1 |
| wu1 | Width dependence of u1 |
| x2u1 | VBS depence of u1 |
| lx2u1 | Length depence of x2u1 |
| wx2u1 | Width depence of x2u1 |
| x3u1 | VDS depence of u1 |
| lx3u1 | Length dependence of x3u1 |
| wx3u1 | Width depence of x3u1 |
| n0 | Subthreshold slope |
| ln0 | Length dependence of n0 |
| wn0 | Width dependence of n0 |
| nb | VBS dependence of subthreshold slope |
| lnb | Length dependence of nb |
| wnb | Width dependence of nb |
| nd | VDS dependence of subthreshold slope |
| lnd | Length dependence of nd |
| wnd | Width dependence of nd |
| tox | Gate oxide thickness in um |
| temp | Temperature in degree Celcius |
| vdd | Supply voltage to specify mus |
| cgso | Gate source overlap capacitance per unit channel width(m) |
| cgdo | Gate drain overlap capacitance per unit channel width(m) |
| cgbo | Gate bulk overlap capacitance per unit channel length(m) |
| xpart | Flag for channel charge partitioning |
| rsh | Source drain diffusion sheet resistance in ohm per square |
| js | Source drain junction saturation current per unit area |
| pb | Source drain junction built in potential |
| mj | Source drain bottom junction capacitance grading coefficient |
| pbsw | Source drain side junction capacitance built in potential |
| mjsw | Source drain side junction capacitance grading coefficient |
| cj | Source drain bottom junction capacitance per unit area |
| cjsw | Source drain side junction capacitance per unit area |
| wdf | Default width of source drain diffusion in um |
| dell | Length reduction of source drain diffusion |

### B.4. BSIM2: Berkeley Short Channel IGFET Model

| BSIM2 — instance input-only parameters | |
|---|---|
| ic | Vector of DS,GS,BS initial voltages |

| BSIM2 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Number of squares in drain |
| nrs | Number of squares in source |
| off | Device is initially off |
| vds | Initial D-S voltage |
| vgs | Initial G-S voltage |
| vbs | Initial B-S voltage |

| BSIM2 — model input-only parameters | |
|---|---|
| nmos | Flag to indicate NMOS |
| pmos | Flag to indicate PMOS |

| BSIM2 — model input-output parameters | |
|---|---|
| vfb | Flat band voltage |
| lvfb | Length dependence of vfb |
| wvfb | Width dependence of vfb |
| phi | Strong inversion surface potential |
| lphi | Length dependence of phi |
| wphi | Width dependence of phi |
| k1 | Bulk effect coefficient 1 |
| lk1 | Length dependence of k1 |
| wk1 | Width dependence of k1 |
| k2 | Bulk effect coefficient 2 |
| lk2 | Length dependence of k2 |
| wk2 | Width dependence of k2 |
| eta0 | VDS dependence of threshold voltage at VDD=0 |
| leta0 | Length dependence of eta0 |
| weta0 | Width dependence of eta0 |
| etab | VBS dependence of eta |
| letab | Length dependence of etab |

*continued*

| BSIM2 — model input-output parameters — *continued* | |
|---|---|
| wetab | Width dependence of etab |
| dl | Channel length reduction in um |
| dw | Channel width reduction in um |
| mu0 | Low-field mobility, at VDS=0 VGS=VTH |
| mu0b | VBS dependence of low-field mobility |
| lmu0b | Length dependence of mu0b |
| wmu0b | Width dependence of mu0b |
| mus0 | Mobility at VDS=VDD VGS=VTH |
| lmus0 | Length dependence of mus0 |
| wmus0 | Width dependence of mus |
| musb | VBS dependence of mus |
| lmusb | Length dependence of musb |
| wmusb | Width dependence of musb |
| mu20 | VDS dependence of mu in tanh term |
| lmu20 | Length dependence of mu20 |
| wmu20 | Width dependence of mu20 |
| mu2b | VBS dependence of mu2 |
| lmu2b | Length dependence of mu2b |
| wmu2b | Width dependence of mu2b |
| mu2g | VGS dependence of mu2 |
| lmu2g | Length dependence of mu2g |
| wmu2g | Width dependence of mu2g |
| mu30 | VDS dependence of mu in linear term |
| lmu30 | Length dependence of mu30 |
| wmu30 | Width dependence of mu30 |
| mu3b | VBS dependence of mu3 |
| lmu3b | Length dependence of mu3b |
| wmu3b | Width dependence of mu3b |
| mu3g | VGS dependence of mu3 |
| lmu3g | Length dependence of mu3g |
| wmu3g | Width dependence of mu3g |
| mu40 | VDS dependence of mu in linear term |
| lmu40 | Length dependence of mu40 |
| wmu40 | Width dependence of mu40 |
| mu4b | VBS dependence of mu4 |
| lmu4b | Length dependence of mu4b |
| wmu4b | Width dependence of mu4b |
| mu4g | VGS dependence of mu4 |
| lmu4g | Length dependence of mu4g |
| wmu4g | Width dependence of mu4g |
| ua0 | Linear VGS dependence of mobility |
| lua0 | Length dependence of ua0 |
| wua0 | Width dependence of ua0 |

*continued*

| BSIM2 — model input-output parameters — *continued* | |
|---|---|
| uab | VBS dependence of ua |
| luab | Length dependence of uab |
| wuab | Width dependence of uab |
| ub0 | Quadratic VGS dependence of mobility |
| lub0 | Length dependence of ub0 |
| wub0 | Width dependence of ub0 |
| ubb | VBS dependence of ub |
| lubb | Length dependence of ubb |
| wubb | Width dependence of ubb |
| u10 | VDS depence of mobility |
| lu10 | Length dependence of u10 |
| wu10 | Width dependence of u10 |
| u1b | VBS depence of u1 |
| lu1b | Length depence of u1b |
| wu1b | Width depence of u1b |
| u1d | VDS depence of u1 |
| lu1d | Length depence of u1d |
| wu1d | Width depence of u1d |
| n0 | Subthreshold slope at VDS=0 VBS=0 |
| ln0 | Length dependence of n0 |
| wn0 | Width dependence of n0 |
| nb | VBS dependence of n |
| lnb | Length dependence of nb |
| wnb | Width dependence of nb |
| nd | VDS dependence of n |
| lnd | Length dependence of nd |
| wnd | Width dependence of nd |
| vof0 | Threshold voltage offset AT VDS=0 VBS=0 |
| lvof0 | Length dependence of vof0 |
| wvof0 | Width dependence of vof0 |
| vofb | VBS dependence of vof |
| lvofb | Length dependence of vofb |
| wvofb | Width dependence of vofb |
| vofd | VDS dependence of vof |
| lvofd | Length dependence of vofd |
| wvofd | Width dependence of vofd |
| ai0 | Pre-factor of hot-electron effect. |
| lai0 | Length dependence of ai0 |
| wai0 | Width dependence of ai0 |
| aib | VBS dependence of ai |
| laib | Length dependence of aib |
| waib | Width dependence of aib |
| bi0 | Exponential factor of hot-electron effect. |

*continued*

| BSIM2 — model input-output parameters — *continued* | |
|---|---|
| lbi0 | Length dependence of bi0 |
| wbi0 | Width dependence of bi0 |
| bib | VBS dependence of bi |
| lbib | Length dependence of bib |
| wbib | Width dependence of bib |
| vghigh | Upper bound of the cubic spline function. |
| lvghigh | Length dependence of vghigh |
| wvghigh | Width dependence of vghigh |
| vglow | Lower bound of the cubic spline function. |
| lvglow | Length dependence of vglow |
| wvglow | Width dependence of vglow |
| tox | Gate oxide thickness in um |
| temp | Temperature in degree Celcius |
| vdd | Maximum Vds |
| vgg | Maximum Vgs |
| vbb | Maximum Vbs |
| cgso | Gate source overlap capacitance per unit channel width(m) |
| cgdo | Gate drain overlap capacitance per unit channel width(m) |
| cgbo | Gate bulk overlap capacitance per unit channel length(m) |
| xpart | Flag for channel charge partitioning |
| rsh | Source drain diffusion sheet resistance in ohm per square |
| js | Source drain junction saturation current per unit area |
| pb | Source drain junction built in potential |
| mj | Source drain bottom junction capacitance grading coefficient |
| pbsw | Source drain side junction capacitance built in potential |
| mjsw | Source drain side junction capacitance grading coefficient |
| cj | Source drain bottom junction capacitance per unit area |
| cjsw | Source drain side junction capacitance per unit area |
| wdf | Default width of source drain diffusion in um |
| dell | Length reduction of source drain diffusion |

### B.5. Capacitor: Fixed capacitor

| Capacitor — instance input-only parameters | |
|---|---|
| sens_cap | flag to request sens. WRT cap. |

| Capacitor — instance input-output parameters | |
|---|---|
| capacitance | Device capacitance |
| ic | Initial capacitor voltage |
| w | Device width |
| l | Device length |

| Capacitor — instance output-only parameters | |
|---|---|
| c | Device current |
| p | Instantaneous device power |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | dc sens. & imag part of ac sens. |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

| Capacitor — model input-only parameters | |
|---|---|
| c | Capacitor model |

| Capacitor — model input-output parameters | |
|---|---|
| cj | Bottom Capacitance per area |
| cjsw | Sidewall capacitance per meter |
| defw | Default width |
| narrow | width correction factor |

### B.6. CCCS: Current controlled current source

| CCCS — instance input-only parameters | |
|---|---|
| sens_gain | flag to request sensitivity WRT gain |

| CCCS — instance input-output parameters | |
|---|---|
| gain | Gain of source |
| control | Name of controlling source |

| CCCS — instance output-only parameters | |
|---|---|
| neg_node | Negative node of source |
| pos_node | Positive node of source |
| c | CCCS current |
| p | CCCS current |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | imag part of ac sensitivity |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

### B.7. CCVS: Linear current controlled current source

| CCVS — instance input-only parameters | |
|---|---|
| sens_trans | flag to request sens. WRT transimpedance |

| CCVS — instance input-output parameters | |
|---|---|
| gain | Transresistance (gain) |
| control | Controlling voltage source |

| CCVS — instance output-only parameters | |
|---|---|
| pos_node | Positive node of source |
| neg_node | Negative node of source |
| c | Device current |
| p | Device power |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | imag part of ac sensitivity |
| sens_mag | sensitivity of ac magnitude |

*continued*

| CCVS — instance output-only parameters — *continued* | |
|---|---|
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

### B.8. CSwitch: Current controlled ideal switch

| CSwitch — instance input-only parameters | |
|---|---|
| on | Initially closed |
| off | Initially open |

| CSwitch — instance input-output parameters | |
|---|---|
| control | Name of controlling source |

| CSwitch — instance output-only parameters | |
|---|---|
| pos_node | Positive node of switch |
| neg_node | Negative node of switch |
| c | Switch current |
| p | Instantaneous power |

| CSwitch — model input-output parameters | |
|---|---|
| csw | Current controlled switch model |
| it | Threshold current |
| ih | Hysterisis current |
| ron | Closed resistance |
| roff | Open resistance |

| CSwitch — model output-only parameters | |
|---|---|
| gon | Closed conductance |
| goff | Open conductance |

### B.9. Diode: Junction Diode model

| Diode — instance input-only parameters | |
|---|---|
| sens_area | flag to request sensitivity WRT area |

| Diode — instance input-output parameters | |
|---|---|
| off | Initially off |
| temp | Instance temperature |
| ic | Initial device voltage |
| area | Area factor |

| Diode — instance output-only parameters | |
|---|---|
| voltage | Diode voltage |
| current | Diode current |
| charge | Diode capacitor charge |
| capcur | Diode capacitor current |
| cond | Diode conductance |
| p | Diode power |
| c | Diode current |
| sens_dc | dc sensitivity |
| sens_real | dc sens. and real part of ac sensitivity |
| sens_imag | imag part of ac sensitivity |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

| Diode — model input-only parameters | |
|---|---|
| d | Diode model |
| kf | flicker noise coefficient |
| af | flicker noise exponent |

| Diode — model input-output parameters | |
|---|---|
| is | Saturation current |
| tnom | Parameter measurement temperature |
| rs | Ohmic resistance |
| n | Emission Coefficient |
| tt | Transit Time |
| cjo | Junction capacitance |
| cj0 | Junction capacitance |
| vj | Junction potential |

*continued*

| Diode — model input-output parameters — *continued* | |
|---|---|
| m | Grading coefficient |
| eg | Activation energy |
| xti | Saturation current temperature exp. |
| fc | Forward bias junction fit parameter |
| bv | Reverse breakdown voltage |
| ibv | Current at reverse breakdown voltage |

| Diode — model output-only parameters | |
|---|---|
| cond | Ohmic conductance |

### B.10. Inductor: Inductors

| Inductor — instance input-only parameters | |
|---|---|
| sens_ind | flag to request sensitivity WRT inductance |

| Inductor — instance input-output parameters | |
|---|---|
| inductance | Inductance of inductor |
| ic | Initial current through inductor |

| Inductor — instance output-only parameters | |
|---|---|
| flux | Flux through inductor |
| volt | Terminal voltage of inductor |
| current | Current through the inductor |
| p | instantaneous power dissipated by the inductor |
| sens_dc | dc sensitivity sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | dc sensitivity and imag part of ac sensitivty |
| sens_mag | sensitivity of AC magnitude |
| sens_ph | sensitivity of AC phase |
| sens_cplx | ac sensitivity |

### B.11. mutual: Mutual inductors

| mutual — instance input-only parameters | |
|---|---|
| sens_coeff | flag to request sensitivity WRT coupling factor |

| mutual — instance input-output parameters | |
|---|---|
| coefficient | Mutual inductance |
| inductor1 | First coupled inductor |
| inductor2 | Second coupled inductor |

| mutual — instance output-only parameters | |
|---|---|
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | dc sensitivity and imag part of ac sensitivty |
| sens_mag | sensitivity of AC magnitude |
| sens_ph | sensitivity of AC phase |
| sens_cplx | ac sensitivity |

### B.12. Isource: Independent current source

| Isource — instance input-only parameters | |
|---|---|
| pulse | Pulse description |
| sine | Sinusoidal source description |
| sin | Sinusoidal source description |
| exp | Exponential source description |
| pwl | Piecewise linear description |
| sffm | single freq. FM description |
| ac | AC magnitude,phase vector |
| p | Power supplied by the source |
| c | Current through current source |
| distof1 | f1 input for distortion |
| distof2 | f2 input for distortion |

| Isource — instance input-output parameters | |
|---|---|
| dc | DC value of source |
| acmag | AC magnitude |
| acphase | AC phase |

| Isource — instance output-only parameters | |
|---|---|
| neg_node | Negative node of source |
| pos_node | Positive node of source |
| acreal | AC real part |
| acimag | AC imaginary part |
| function | Function of the source |
| order | Order of the source function |
| coeffs | Coefficients of the source |

### B.13. JFET: Junction Field effect transistor

| JFET — instance input-output parameters | |
|---|---|
| off | Device initially off |
| ic | Initial VDS,VGS vector |
| area | Area factor |
| ic-vds | Initial D-S voltage |
| ic-vgs | Initial G-S volrage |
| temp | Instance temperature |

| JFET — instance output-only parameters | |
|---|---|
| drain-node | Number of drain node |
| gate-node | Number of gate node |
| source-node | Number of source node |
| drain-prime-node | Internal drain node |
| source-prime-node | Internal source node |
| vgs | Voltage G-S |
| vgd | Voltage G-D |
| cg | Current at gate node |
| cd | Current at drain node |
| cgd | Current G-D |
| gm | Transconductance |
| gds | Conductance D-S |
| ggs | Conductance G-S |
| ggd | Conductance G-D |
| qgs | Charge storage G-S junction |
| cqgs | Capacitance due to charge storage G-S junction |

*continued*

| JFET — instance output-only parameters — *continued* | |
|---|---|
| qgd | Charge storage G-D junction |
| cqgd | Capacitance due to charge storage G-D junction |
| cs | Source current |
| p | Power dissipated by the JFET |
| kf | Flicker Noise Coefficient |
| af | Flicker Noise Exponent |

| JFET — model input-output parameters | |
|---|---|
| vt0 | Threshold voltage |
| vto | Threshold voltage |
| beta | Transconductance parameter |
| lambda | Channel length modulation param. |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |
| cgs | G-S junction capactance |
| cgd | G-D junction cap |
| pb | Gate junction potential |
| is | Gate junction saturation current |
| fc | Forward bias junction fir parm. |
| njf | N type JFET model |
| pjf | P type JFET model |
| tnom | parameter measurement temperature |

| JFET — model output-only parameters | |
|---|---|
| drainconduct | Drain conductance |
| sourceconduct | Source conductance |

### B.14. LTRA: Lossy transmission line

| LTRA — instance input-only parameters | |
|---|---|
| ic | Initial condition vector:v1,i1,v2,i2 |

| LTRA — instance input-output parameters | |
|---|---|
| v1 | Initial voltage at end 1 |
| v2 | Initial voltage at end 2 |
| i1 | Initial current at end 1 |
| i2 | Initial current at end 2 |

| LTRA — instance output-only parameters | |
|---|---|
| pos_node1 | Positive node of end 1 of t. line |
| neg_node1 | Negative node of end 1 of t. line |
| pos_node2 | Positive node of end 2 of t. line |
| neg_node2 | Negative node of end 2 of t. line |

| LTRA — model input-output parameters | |
|---|---|
| ltra | LTRA model |
| r | Resistance per metre |
| l | Inductance per metre |
| g | Conductance per metre |
| c | Capacitance per metre |
| len | length of line |
| nocontrol | No timestep control |
| steplimit | always limit timestep to 0.8*(delay of line) |
| nosteplimit | don't always limit timestep to 0.8*(delay of line) |
| lininterp | use linear interpolation |
| quadinterp | use quadratic interpolation |
| mixedinterp | use linear interpolation only if quadratic interpolation results look unacceptable |
| truncnr | use N-R iterations for step calculation in LTRAtrunc |
| truncdontcut | don't limit timestep to keep impulse response calculation errors low |
| compactrel | special reltol for straight line checking |
| compactabs | special abstol for straight line checking |

| LTRA — model output-only parameters | |
|---|---|
| rel | Rel. rate of change of deriv. for bkpt |
| abs | Abs. rate of change of deriv. for bkpt |

### B.15. MES: GaAs MESFET model

| MES — instance input-output parameters | |
|---|---|
| area | Area factor |
| icvds | Initial D-S voltage |
| icvgs | Initial G-S voltage |

| MES — instance output-only parameters | |
|---|---|
| off | Device initially off |
| dnode | Number of drain node |
| gnode | Number of gate node |
| snode | Number of source node |
| dprimenode | Number of internal drain node |
| sprimenode | Number of internal source node |
| vgs | Gate-Source voltage |
| vgd | Gate-Drain voltage |
| cg | Gate capacitance |
| cd | Drain capacitance |
| cgd | Gate_Drain capacitance |
| gm | Transconductance |
| gds | Drain-Source conductance |
| ggs | Gate-Source conductance |
| ggd | Gate-Drain conductance |
| qgs | Gate-Source charge storage |
| cqgs | Capacitance due to gate-source charge storage |
| qgd | Gate-Drain charge storage |
| cqgd | Capacitance due to gate-drain charge storage |
| cs | Source current |
| p | Power dissipated by the mesfet |

| MES — model input-output parameters | |
|---|---|
| vt0 | Pinch-off voltage |
| vto | Pinch-off voltage |
| alpha | Saturation voltage parameter |
| beta | Transconductance parameter |
| lambda | Channel length modulation parm. |
| b | Doping tail extending parameter |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |
| cgs | G-S junction capacitance |
| cgd | G-D junction capacitance |
| pb | Gate junction potential |
| is | Junction saturation current |
| fc | Forward biad junction fit parm. |

| MES — model output-only parameters | |
|---|---|
| nmf | N type MESfet model |
| pmf | P type MESfet model |
| gd | Drain conductance |
| gs | Source conductance |
| depl_cap | Depletion capacitance |
| vcrit | Critical voltage |

### B.16. Mos1: Level 1 MOSfet model with Meyer capacitance model

| Mos1 — instance input-only parameters | |
|---|---|
| off | Device initially off |
| ic | Vector of D-S, G-S, B-S voltages |
| sens_l | flag to request sensitivity WRT length |
| sens_w | flag to request sensitivity WRT width |

| Mos1 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Drain squares |
| nrs | Source squares |
| icvds | Initial D-S voltage |
| icvgs | Initial G-S voltage |
| icvbs | Initial B-S voltage |
| temp | Instance temperature |

| Mos1 — instance output-only parameters | |
|---|---|
| cgs | Gate-Source capacitance |
| cgd | Gate-Drain capacitance |
| dnode | Number of the drain node |
| gnode | Number of the gate node |
| snode | Number of the source node |
| bnode | Number of the node |
| dnodeprime | Number of int. drain node |
| snodeprime | Number of int. source node |
| sourceconductance | Conductance of source |
| drainconductance | Conductance of drain |

*continued*

| Mos1 — instance output-only parameters — *continued* | |
|---|---|
| von | |
| vdsat | Saturation drain voltage |
| sourcevcrit | Critical source voltage |
| drainvcrit | Critical drain voltage |
| cd | Drain current |
| cbs | B-S junction capacitance |
| cbd | B-D junction capacitance |
| gmbs | Bulk-Source transconductance |
| gm | Transconductance |
| gds | Drain-Source conductance |
| gbd | Bulk-Drain conductance |
| gbs | Bulk-Source conductance |
| capbd | Bulk-Drain capacitance |
| capbs | Bulk-Source capacitance |
| cbd0 | Zero-Bias B-D junction capacitance |
| cbdsw0 | |
| cbs0 | Zero-Bias B-S junction capacitance |
| cbssw0 | |
| vbd | Bulk-Drain voltage |
| vbs | Bulk-Source voltage |
| vgs | Gate-Source voltage |
| vds | Drain-Source voltage |
| capgs | Gate-Source capacitance |
| qgs | Gate-Source charge storage |
| cqgs | Capacitance due to gate-source charge storage |
| capgd | Gate-Drain capacitance |
| qgd | Gate-Drain charge storage |
| cqgd | Capacitance due to gate-drain charge storage |
| capgb | Gate-Bulk capacitance |
| qgb | Gate-Bulk charge storage |
| cqgb | Capacitance due to gate-bulk charge storage |
| qbd | Bulk-Drain charge storage |
| cqbd | Capacitance due to bulk-drain charge storage |
| qbs | Bulk-Source charge storage |
| cqbs | Capacitance due to bulk-source charge storage |
| cs | Source current |
| cg | Gate current |
| cb | Bulk current |
| p | Instaneous power |
| sens_l_dc | dc sensitivity wrt length |
| sens_l_real | real part of ac sensitivity wrt length |
| sens_l_imag | imag part of ac sensitivity wrt length |
| sens_l_mag | sensitivity wrt l of ac magnitude |

*continued*

| Mos1 — instance output-only parameters — *continued* | |
|---|---|
| sens_l_ph | sensitivity wrt l of ac phase |
| sens_l_cplx | ac sensitivity wrt length |
| sens_w_dc | dc sensitivity wrt width |
| sens_w_real | real part of ac sensitivity wrt width |
| sens_w_imag | imag part of ac sensitivity wrt width |
| sens_w_mag | sensitivity wrt w of ac magnitude |
| sens_w_ph | sensitivity wrt w of ac phase |
| sens_w_cplx | ac sensitivity wrt width |

| Mos1 — model input-only parameters | |
|---|---|
| nmos | N type MOSfet model |
| pmos | P type MOSfet model |
| kf | Flicker noise coefficient |
| af | Flicker noise exponent |

| Mos1 — model input-output parameters | |
|---|---|
| vto | Threshold voltage |
| vt0 | Threshold voltage |
| kp | Transconductance parameter |
| gamma | Bulk threshold parameter |
| phi | Surface potential |
| lambda | Channel length modulation |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |
| cbd | B-D junction capacitance |
| cbs | B-S junction capacitance |
| is | Bulk junction sat. current |
| pb | Bulk junction potential |
| cgso | Gate-source overlap cap. |
| cgdo | Gate-drain overlap cap. |
| cgbo | Gate-bulk overlap cap. |
| rsh | Sheet resistance |
| cj | Bottom junction cap per area |
| mj | Bottom grading coefficient |
| cjsw | Side junction cap per area |
| mjsw | Side grading coefficient |
| js | Bulk jct. sat. current density |
| tox | Oxide thickness |
| ld | Lateral diffusion |
| u0 | Surface mobility |
| uo | Surface mobility |
| fc | Forward bias jct. fit parm. |

*continued*

| Mos1 — model input-output parameters — *continued* | |
|---|---|
| nsub | Substrate doping |
| tpg | Gate type |
| nss | Surface state density |
| tnom | Parameter measurement temperature |

### B.17. Mos2: Level 2 MOSfet model with Meyer capacitance model

| Mos2 — instance input-only parameters | |
|---|---|
| off | Device initially off |
| ic | Vector of D-S, G-S, B-S voltages |
| sens_l | flag to request sensitivity WRT length |
| sens_w | flag to request sensitivity WRT width |

| Mos2 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Drain squares |
| nrs | Source squares |
| icvds | Initial D-S voltage |
| icvgs | Initial G-S voltage |
| icvbs | Initial B-S voltage |
| temp | Instance operating temperature |

| Mos2 — instance output-only parameters | |
|---|---|
| cgs | Gate-Source capacitance |
| cgd | Gate-Drain capacitance |
| dnode | Number of drain node |
| gnode | Number of gate node |
| snode | Number of source node |
| bnode | Number of bulk node |
| dnodeprime | Number of internal drain node |
| snodeprime | Number of internal source node |
| sourceconductance | Source conductance |
| drainconductance | Drain conductance |
| von | |
| vdsat | Saturation drain voltage |
| sourcevcrit | Critical source voltage |

*continued*

| Mos2 — instance output-only parameters — *continued* | |
|---|---|
| drainvcrit | Critical drain voltage |
| cd | Drain current |
| cbs | B-S junction capacitance |
| cbd | B-D junction capacitance |
| gmbs | Bulk-Source transconductance |
| gm | Transconductance |
| gds | Drain-Source conductance |
| gbd | Bulk-Drain conductance |
| gbs | Bulk-Source conductance |
| capbd | Bulk-Drain capacitance |
| capbs | Bulk-Source capacitance |
| cbd0 | Zero-Bias B-D junction capacitance |
| cbdsw0 | |
| cbs0 | Zero-Bias B-S junction capacitance |
| cbssw0 | |
| vbd | Bulk-Drain voltage |
| vbs | Bulk-Source voltage |
| vgs | Gate-Source voltage |
| vds | Drain-Source voltage |
| capgs | Gate-Source capacitance |
| qgs | Gate-Source charge storage |
| cqgs | Capacitance due to gate-source charge storage |
| capgd | Gate-Drain capacitance |
| qgd | Gate-Drain charge storage |
| cqgd | Capacitance due to gate-drain charge storage |
| capgb | Gate-Bulk capacitance |
| qgb | Gate-Bulk charge storage |
| cqgb | Capacitance due to gate-bulk charge storage |
| qbd | Bulk-Drain charge storage |
| cqbd | Capacitance due to bulk-drain charge storage |
| qbs | Bulk-Source charge storage |
| cqbs | Capacitance due to bulk-source charge storage |
| cs | Source current |
| cg | Gate current |
| cb | Bulk current |
| p | Instantaneous power |
| sens_l_dc | dc sensitivity wrt length |
| sens_l_real | real part of ac sensitivity wrt length |
| sens_l_imag | imag part of ac sensitivity wrt length |
| sens_l_cplx | ac sensitivity wrt length |
| sens_l_mag | sensitivity wrt l of ac magnitude |
| sens_l_ph | sensitivity wrt l of ac phase |
| sens_w_dc | dc sensitivity wrt width |

*continued*

| Mos2 — instance output-only parameters — *continued* | |
|---|---|
| sens_w_real | dc sensitivity and real part of ac sensitivity wrt width |
| sens_w_imag | imag part of ac sensitivity wrt width |
| sens_w_mag | sensitivity wrt w of ac magnitude |
| sens_w_ph | sensitivity wrt w of ac phase |
| sens_w_cplx | ac sensitivity wrt width |

| Mos2 — model input-only parameters | |
|---|---|
| nmos | N type MOSfet model |
| pmos | P type MOSfet model |
| kf | Flicker noise coefficient |
| af | Flicker noise exponent |

| Mos2 — model input-output parameters | |
|---|---|
| vto | Threshold voltage |
| vt0 | Threshold voltage |
| kp | Transconductance parameter |
| gamma | Bulk threshold parameter |
| phi | Surface potential |
| lambda | Channel length modulation |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |
| cbd | B-D junction capacitance |
| cbs | B-S junction capacitance |
| is | Bulk junction sat. current |
| pb | Bulk junction potential |
| cgso | Gate-source overlap cap. |
| cgdo | Gate-drain overlap cap. |
| cgbo | Gate-bulk overlap cap. |
| rsh | Sheet resistance |
| cj | Bottom junction cap per area |
| mj | Bottom grading coefficient |
| cjsw | Side junction cap per area |
| mjsw | Side grading coefficient |
| js | Bulk jct. sat. current density |
| tox | Oxide thickness |
| ld | Lateral diffusion |
| u0 | Surface mobility |
| uo | Surface mobility |
| fc | Forward bias jct. fit parm. |
| nsub | Substrate doping |
| tpg | Gate type |
| nss | Surface state density |

*continued*

| Mos2 — model input-output parameters — *continued* | |
|---|---|
| delta | Width effect on threshold |
| uexp | Crit. field exp for mob. deg. |
| ucrit | Crit. field for mob. degradation |
| vmax | Maximum carrier drift velocity |
| xj | Junction depth |
| neff | Total channel charge coeff. |
| nfs | Fast surface state density |
| tnom | Parameter measurement temperature |

### B.18. Mos3: Level 3 MOSfet model with Meyer capacitance model

| Mos3 — instance input-only parameters | |
|---|---|
| off | Device initially off |
| sens_l | flag to request sensitivity WRT length |
| sens_w | flag to request sensitivity WRT width |

| Mos3 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Drain squares |
| nrs | Source squares |
| icvds | Initial D-S voltage |
| icvgs | Initial G-S voltage |
| icvbs | Initial B-S voltage |
| ic | Vector of D-S, G-S, B-S voltages |
| temp | Instance operating temperature |

| Mos3 — instance output-only parameters | |
|---|---|
| cgs | Gate-Source capacitance |
| cgd | Gate-Drain capacitance |
| dnode | Number of drain node |
| gnode | Number of gate node |
| snode | Number of source node |
| bnode | Number of bulk node |
| dnodeprime | Number of internal drain node |
| snodeprime | Number of internal source node |
| sourceconductance | Source conductance |

*continued*

| Mos3 — instance output-only parameters — *continued* | |
|---|---|
| drainconductance | Drain conductance |
| von | |
| vdsat | Saturation drain voltage |
| sourcevcrit | Critical source voltage |
| drainvcrit | Critical drain voltage |
| cd | Drain current |
| cbs | B-S junction capacitance |
| cbd | B-D junction capacitance |
| gmbs | Bulk-Source transconductance |
| gm | Transconductance |
| gds | Drain-Source conductance |
| gbd | Bulk-Drain conductance |
| gbs | Bulk-Source conductance |
| capbd | Bulk-Drain capacitance |
| capbs | Bulk-Source capacitance |
| cbd0 | Zero-Bias B-D junction capacitance |
| cbdsw0 | |
| cbs0 | Zero-Bias B-S junction capacitance |
| cbssw0 | |
| vbd | Bulk-Drain voltage |
| vbs | Bulk-Source voltage |
| vgs | Gate-Source voltage |
| vds | Drain-Source voltage |
| capgs | Gate-Source capacitance |
| qgs | Gate-Source charge storage |
| cqgs | Capacitance due to gate-source charge storage |
| capgd | Gate-Drain capacitance |
| qgd | Gate-Drain charge storage |
| cqgd | Capacitance due to gate-drain charge storage |
| capgb | Gate-Bulk capacitance |
| qgb | Gate-Bulk charge storage |
| cqgb | Capacitance due to gate-bulk charge storage |
| qbd | Bulk-Drain charge storage |
| cqbd | Capacitance due to bulk-drain charge storage |
| qbs | Bulk-Source charge storage |
| cqbs | Capacitance due to bulk-source charge storage |
| cs | Source current |
| cg | Gate current |
| cb | Bulk current |
| p | Instantaneous power |
| sens_l_dc | dc sensitivity wrt length |
| sens_l_real | real part of ac sensitivity wrt length |
| sens_l_imag | imag part of ac sensitivity wrt length |

*continued*

| Mos3 — instance output-only parameters — *continued* | |
|---|---|
| sens_l_cplx | ac sensitivity wrt length |
| sens_l_mag | sensitivity wrt l of ac magnitude |
| sens_l_ph | sensitivity wrt l of ac phase |
| sens_w_dc | dc sensitivity wrt width |
| sens_w_real | real part of ac sensitivity wrt width |
| sens_w_imag | imag part of ac sensitivity wrt width |
| sens_w_mag | sensitivity wrt w of ac magnitude |
| sens_w_ph | sensitivity wrt w of ac phase |
| sens_w_cplx | ac sensitivity wrt width |

| Mos3 — model input-only parameters | |
|---|---|
| nmos | N type MOSfet model |
| pmos | P type MOSfet model |
| kf | Flicker noise coefficient |
| af | Flicker noise exponent |

| Mos3 — model input-output parameters | |
|---|---|
| vto | Threshold voltage |
| vt0 | Threshold voltage |
| kp | Transconductance parameter |
| gamma | Bulk threshold parameter |
| phi | Surface potential |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |
| cbd | B-D junction capacitance |
| cbs | B-S junction capacitance |
| is | Bulk junction sat. current |
| pb | Bulk junction potential |
| cgso | Gate-source overlap cap. |
| cgdo | Gate-drain overlap cap. |
| cgbo | Gate-bulk overlap cap. |
| rsh | Sheet resistance |
| cj | Bottom junction cap per area |
| mj | Bottom grading coefficient |
| cjsw | Side junction cap per area |
| mjsw | Side grading coefficient |
| js | Bulk jct. sat. current density |
| tox | Oxide thickness |
| ld | Lateral diffusion |
| u0 | Surface mobility |
| uo | Surface mobility |
| fc | Forward bias jct. fit parm. |

*continued*

| Mos3 — model input-output parameters — *continued* | |
|---|---|
| nsub | Substrate doping |
| tpg | Gate type |
| nss | Surface state density |
| delta | Width effect on threshold |
| vmax | Maximum carrier drift velocity |
| xj | Junction depth |
| nfs | Fast surface state density |
| eta | |
| xd | Depletion layer width |
| input_delta | Input delta |
| theta | Theta |
| alpha | Alpha |
| kappa | Kappa |
| tnom | Parameter measurement temperature |

## B.19. Mos6: Level 6 MOSfet model with Meyer capacitance model

| Mos6 — instance input-only parameters | |
|---|---|
| off | Device initially off |
| ic | Vector of D-S, G-S, B-S voltages |
| sens_l | flag to request sensitivity WRT length |
| sens_w | flag to request sensitivity WRT width |

| Mos6 — instance input-output parameters | |
|---|---|
| l | Length |
| w | Width |
| ad | Drain area |
| as | Source area |
| pd | Drain perimeter |
| ps | Source perimeter |
| nrd | Drain squares |
| nrs | Source squares |
| icvds | Initial D-S voltage |
| icvgs | Initial G-S voltage |
| icvbs | Initial B-S voltage |
| temp | Instance temperature |

| Mos6 — instance output-only parameters | |
|---|---|
| cgs | Gate-Source capacitance |
| cgd | Gate-Drain capacitance |
| dnode | Number of the drain node |
| gnode | Number of the gate node |
| snode | Number of the source node |
| bnode | Number of the node |
| dnodeprime | Number of int. drain node |
| snodeprime | Number of int. source node |
| sourceconductance | Conductance of source |
| drainconductance | Conductance of drain |
| von | |
| vdsat | Saturation drain voltage |
| sourcevcrit | Critical source voltage |
| drainvcrit | Critical drain voltage |
| cd | Drain current |
| cbs | B-S junction capacitance |
| cbd | B-D junction capacitance |
| gmbs | Bulk-Source transconductance |
| gm | Transconductance |
| gds | Drain-Source conductance |
| gbd | Bulk-Drain conductance |
| gbs | Bulk-Source conductance |
| capbd | Bulk-Drain capacitance |
| capbs | Bulk-Source capacitance |
| cbd0 | Zero-Bias B-D junction capacitance |
| cbdsw0 | |
| cbs0 | Zero-Bias B-S junction capacitance |
| cbssw0 | |
| vbd | Bulk-Drain voltage |
| vbs | Bulk-Source voltage |
| vgs | Gate-Source voltage |
| vds | Drain-Source voltage |
| capgs | Gate-Source capacitance |
| qgs | Gate-Source charge storage |
| cqgs | Capacitance due to gate-source charge storage |
| capgd | Gate-Drain capacitance |
| qgd | Gate-Drain charge storage |
| cqgd | Capacitance due to gate-drain charge storage |
| capgb | Gate-Bulk capacitance |
| qgb | Gate-Bulk charge storage |
| cqgb | Capacitance due to gate-bulk charge storage |
| qbd | Bulk-Drain charge storage |

*continued*

| Mos6 — instance output-only parameters — *continued* | |
|---|---|
| cqbd | Capacitance due to bulk-drain charge storage |
| qbs | Bulk-Source charge storage |
| cqbs | Capacitance due to bulk-source charge storage |
| cs | Source current |
| cg | Gate current |
| cb | Bulk current |
| p | Instaneous power |
| sens_l_dc | dc sensitivity wrt length |
| sens_l_real | real part of ac sensitivity wrt length |
| sens_l_imag | imag part of ac sensitivity wrt length |
| sens_l_mag | sensitivity wrt l of ac magnitude |
| sens_l_ph | sensitivity wrt l of ac phase |
| sens_l_cplx | ac sensitivity wrt length |
| sens_w_dc | dc sensitivity wrt width |
| sens_w_real | real part of ac sensitivity wrt width |
| sens_w_imag | imag part of ac sensitivity wrt width |
| sens_w_mag | sensitivity wrt w of ac magnitude |
| sens_w_ph | sensitivity wrt w of ac phase |
| sens_w_cplx | ac sensitivity wrt width |

| Mos6 — model input-only parameters | |
|---|---|
| nmos | N type MOSfet model |
| pmos | P type MOSfet model |

| Mos6 — model input-output parameters | |
|---|---|
| vto | Threshold voltage |
| vt0 | Threshold voltage |
| kv | Saturation voltage factor |
| nv | Saturation voltage coeff. |
| kc | Saturation current factor |
| nc | Saturation current coeff. |
| nvth | Threshold voltage coeff. |
| ps | Sat. current modification par. |
| gamma | Bulk threshold parameter |
| gamma1 | Bulk threshold parameter 1 |
| sigma | Static feedback effect par. |
| phi | Surface potential |
| lambda | Channel length modulation param. |
| lambda0 | Channel length modulation param. 0 |
| lambda1 | Channel length modulation param. 1 |
| rd | Drain ohmic resistance |
| rs | Source ohmic resistance |

*continued*

| Mos6 — model input-output parameters — *continued* | |
|---|---|
| cbd | B-D junction capacitance |
| cbs | B-S junction capacitance |
| is | Bulk junction sat. current |
| pb | Bulk junction potential |
| cgso | Gate-source overlap cap. |
| cgdo | Gate-drain overlap cap. |
| cgbo | Gate-bulk overlap cap. |
| rsh | Sheet resistance |
| cj | Bottom junction cap per area |
| mj | Bottom grading coefficient |
| cjsw | Side junction cap per area |
| mjsw | Side grading coefficient |
| js | Bulk jct. sat. current density |
| ld | Lateral diffusion |
| tox | Oxide thickness |
| u0 | Surface mobility |
| uo | Surface mobility |
| fc | Forward bias jct. fit parm. |
| tpg | Gate type |
| nsub | Substrate doping |
| nss | Surface state density |
| tnom | Parameter measurement temperature |

### B.20. Resistor: Simple linear resistor

| Resistor — instance input-only parameters | |
|---|---|
| sens_resist | flag to request sensitivity WRT resistance |

| Resistor — instance input-output parameters | |
|---|---|
| resistance | Resistance |
| w | Width |
| l | Length |
| c | Current |
| p | Power |
| temp | Instance operating temperature |

| Resistor — instance output-only parameters | |
|---|---|
| sens_dc | dc sensitivity |
| sens_real | dc sensitivity and real part of ac sensitivity |
| sens_imag | dc sensitivity and imag part of ac sensitivity |
| sens_mag | ac sensitivity of magnitude |
| sens_ph | ac sensitivity of phase |
| sens_cplx | ac sensitivity |

| Resistor — model input-only parameters | |
|---|---|
| r | Device is a resistor model |

| Resistor — model input-output parameters | |
|---|---|
| tc1 | First order temp. coefficient |
| tc2 | Second order temp. coefficient |
| rsh | Sheet resistance |
| defw | Default device width |
| narrow | Narrowing of resistor |
| tnom | Parameter measurement temperature |

### B.21. Switch: Ideal voltage controlled switch

| Switch — instance input-only parameters | |
|---|---|
| on | Switch initially closed |
| off | Switch initially open |

| Switch — instance input-output parameters | |
|---|---|
| pos_node | Positive node of switch |
| neg_node | Negative node of switch |

| Switch — instance output-only parameters | |
|---|---|
| cont_p_node | Positive contr. node of switch |
| cont_n_node | Positive contr. node of switch |
| c | Switch current |
| p | Switch power |

| Switch — model input-output parameters | |
|---|---|
| sw | Switch model |
| vt | Threshold voltage |
| vh | Hysteresis voltage |
| ron | Resistance when closed |
| roff | Resistance when open |

| Switch — model output-only parameters | |
|---|---|
| gon | Conductance when closed |
| goff | Conductance when open |

### B.22. Tranline: Lossless transmission line

| Tranline — instance input-only parameters | |
|---|---|
| ic | Initial condition vector:v1,i1,v2,i2 |

| Tranline — instance input-output parameters | |
|---|---|
| z0 | Characteristic impedance |
| zo | Characteristic impedance |
| f | Frequency |
| td | Transmission delay |
| nl | Normalized length at frequency given |
| v1 | Initial voltage at end 1 |
| v2 | Initial voltage at end 2 |
| i1 | Initial current at end 1 |
| i2 | Initial current at end 2 |

| Tranline — instance output-only parameters | |
|---|---|
| rel | Rel. rate of change of deriv. for bkpt |
| abs | Abs. rate of change of deriv. for bkpt |
| pos_node1 | Positive node of end 1 of t. line |
| neg_node1 | Negative node of end 1 of t. line |
| pos_node2 | Positive node of end 2 of t. line |
| neg_node2 | Negative node of end 2 of t. line |
| delays | Delayed values of excitation |

### B.23. URC: Uniform R.C. line

| URC — instance input-output parameters | |
|---|---|
| l | Length of transmission line |
| n | Number of lumps |

| URC — instance output-only parameters | |
|---|---|
| pos_node | Positive node of URC |
| neg_node | Negative node of URC |
| gnd | Ground node of URC |

| URC — model input-only parameters | |
|---|---|
| urc | Uniform R.C. line model |

| URC — model input-output parameters | |
|---|---|
| k | Propagation constant |
| fmax | Maximum frequency of interest |
| rperl | Resistance per unit length |
| cperl | Capacitance per unit length |
| isperl | Saturation current per length |
| rsperl | Diode resistance per length |

### B.24. VCCS: Voltage controlled current source

| VCCS — instance input-only parameters | |
|---|---|
| sens_trans | flag to request sensitivity WRT transconductance |
| ic | Initial condition of controlling source |

| VCCS — instance input-output parameters | |
|---|---|
| gain | Transconductance of source (gain) |

| VCCS — instance output-only parameters | |
|---|---|
| pos_node | Positive node of source |
| neg_node | Negative node of source |
| cont_p_node | Positive node of contr. source |
| cont_n_node | Negative node of contr. source |
| c | Current |
| p | Power |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | imag part of ac sensitivity |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

### B.25. VCVS: Voltage controlled voltage source

| VCVS — instance input-only parameters | |
|---|---|
| sens_gain | flag to request sensitivity WRT gain |
| ic | Initial condition of controlling source |

| VCVS — instance input-output parameters | |
|---|---|
| gain | Voltage gain |

| VCVS — instance output-only parameters | |
|---|---|
| pos_node | Positive node of source |
| neg_node | Negative node of source |
| cont_p_node | Positive node of contr. source |
| cont_n_node | Negative node of contr. source |
| c | Current |
| p | Power |
| sens_dc | dc sensitivity |
| sens_real | real part of ac sensitivity |
| sens_imag | imag part of ac sensitivity |
| sens_mag | sensitivity of ac magnitude |
| sens_ph | sensitivity of ac phase |
| sens_cplx | ac sensitivity |

### B.26. Vsource: Independent voltage source

| Vsource — instance input-only parameters | |
|---|---|
| pulse | Pulse description |
| sine | Sinusoidal source description |
| sin | Sinusoidal source description |
| exp | Exponential source description |
| pwl | Piecewise linear description |
| sffm | Single freq. FM descripton |
| ac | AC magnitude, phase vector |
| distof1 | f1 input for distortion |
| distof2 | f2 input for distortion |

| Vsource — instance input-output parameters | |
|---|---|
| dc | D.C. source value |
| acmag | A.C. Magnitude |
| acphase | A.C. Phase |

| Vsource — instance output-only parameters | |
|---|---|
| pos_node | Positive node of source |
| neg_node | Negative node of source |
| function | Function of the source |
| order | Order of the source function |
| coeffs | Coefficients for the function |
| acreal | AC real part |
| acimag | AC imaginary part |
| c | Voltage source current |
| p | Instantaneous power |